

# Planar Josephson junction devices with narrow superconducting strips: Topological properties and optimization

*Tudor D. Stanescu*

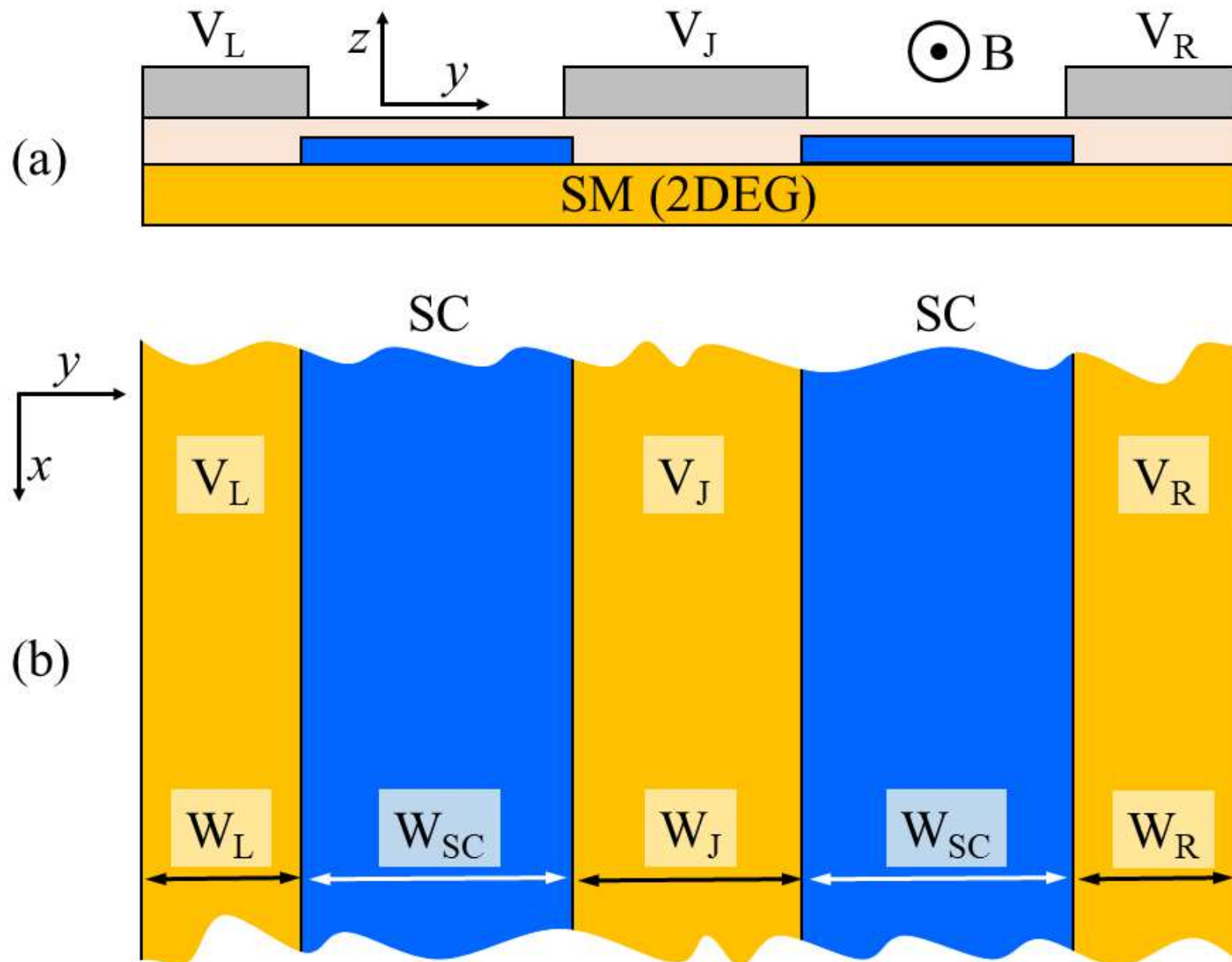
West Virginia University

*Purna Paudel* (WVU)

*Javad Shabani* (NYU)



# Hybrid device & modeling



# Theoretical approach

$$H = H_{SM} + H_{SC} + H_{SM-SC},$$

## Green's function method

$$G_{SM}(\omega, k) = [\omega - \mathcal{H}_{SM}(k) - \Sigma_{SC}(\omega, k)]^{-1}$$

$$\Sigma_{SC}(\omega) = -\frac{\gamma}{\sqrt{\Delta_0^2 - \omega^2}} \left( \omega \sigma_0 \tau_0 \mathbb{I}_{SC}^0 + \Delta_0 \sigma_y \tau_y \mathbb{I}_{SC}^\phi \right)$$

$$\text{with: } [\mathbb{I}_{SC}^0]_{jj} = 1 \quad [\mathbb{I}_{SC}^\phi]_{jj} = e^{\pm i\phi/2}$$

$$A(\omega, k; j) = -\frac{1}{\pi} \text{Im Tr}[G_{SM}(\omega + i\eta, k)]_{jj},$$

DOS

$$\rho(\omega) = \sum_{k,j} A(\omega, k; j),$$

LDOS

$$\rho(\omega, j) = \sum_k A(\omega, k; j).$$

## Effective Hamiltonian

$$\sqrt{\Delta_0^2 - \omega^2} \approx \Delta_0$$

$$[\mathcal{H}_{eff}(k)]_{jj'} = \begin{cases} [\mathcal{H}_{SC}]_{jj'}; & j, j' \in SM, \\ Z [\mathcal{H}_{SC}]_{jj'} - \Delta \sigma_y \tau_y \delta_{jj'}; & j, j' \in SC, \\ Z^{\frac{1}{2}} [\mathcal{H}_{SC}]_{jj'}; & j(j') \in SM, j'(j) \in SC, \end{cases}$$

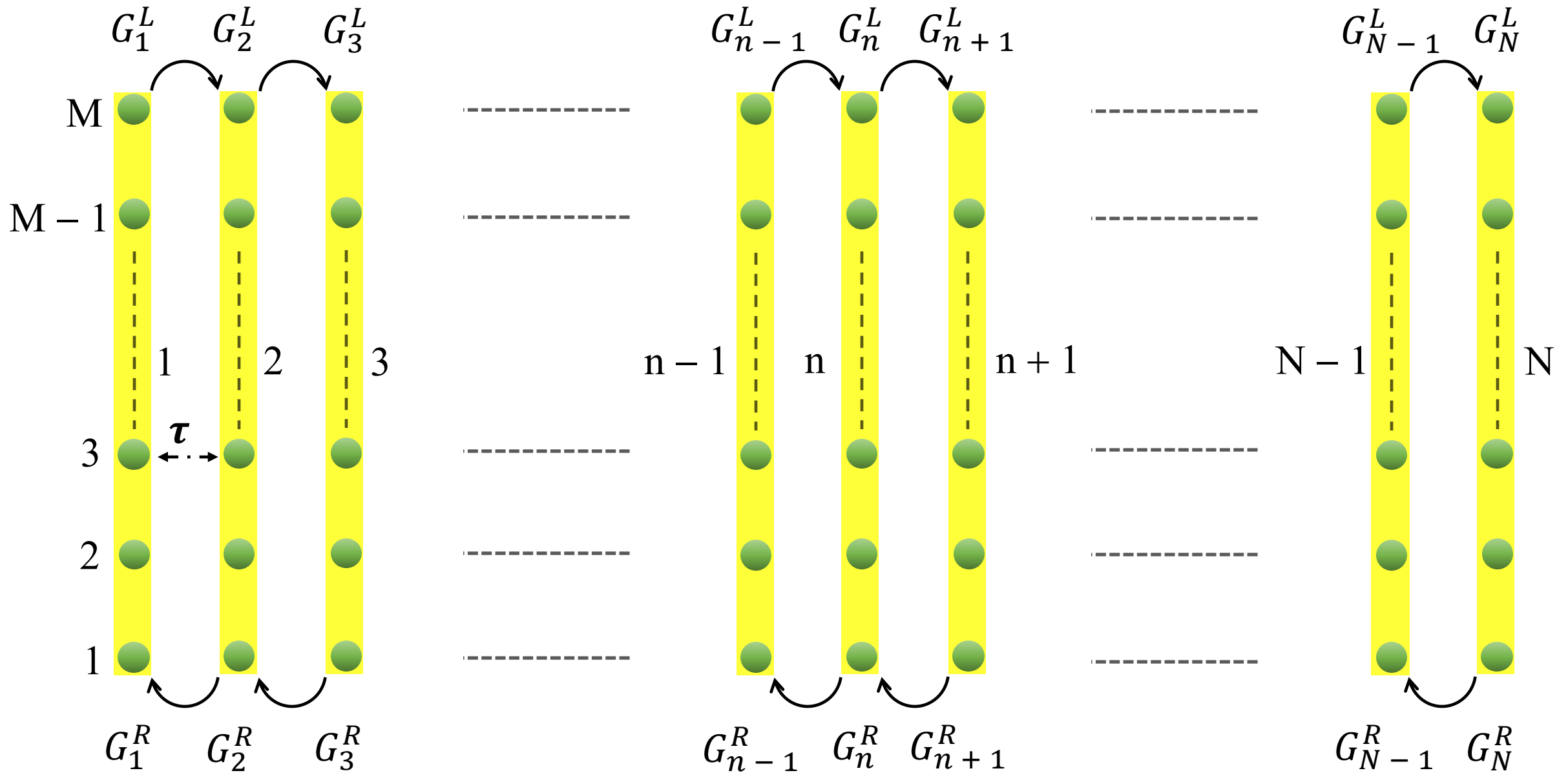
$$\text{with: } \Delta = \gamma \Delta_0 / (\gamma + \Delta_0) e^{\pm i\phi/2}$$

$$Z = \Delta_0 / (\Delta_0 + \gamma)$$

$Z_2$  topological invariant:

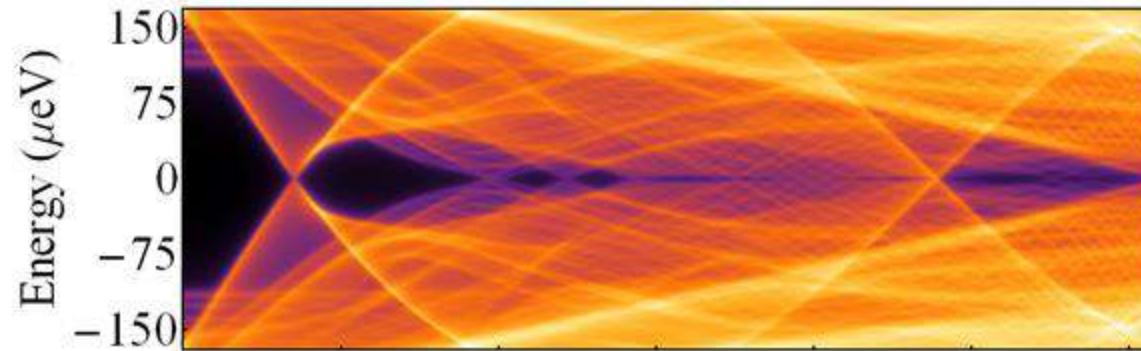
$$\nu = \text{sign}\{\text{Pf}[H_{eff}(0)U_C]\} \text{sign}\{\text{Pf}[H_{eff}(\pi)U_C]\} = \pm 1,$$

# Recursive Green's function formalism

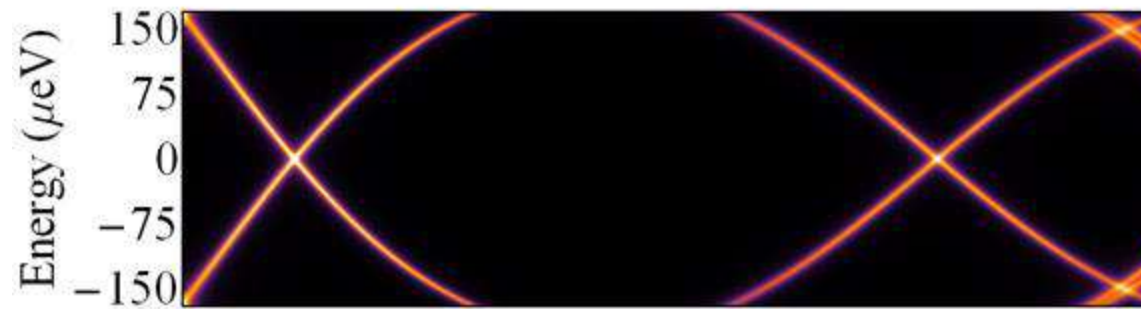


# Low-energy spectral features (comparison)

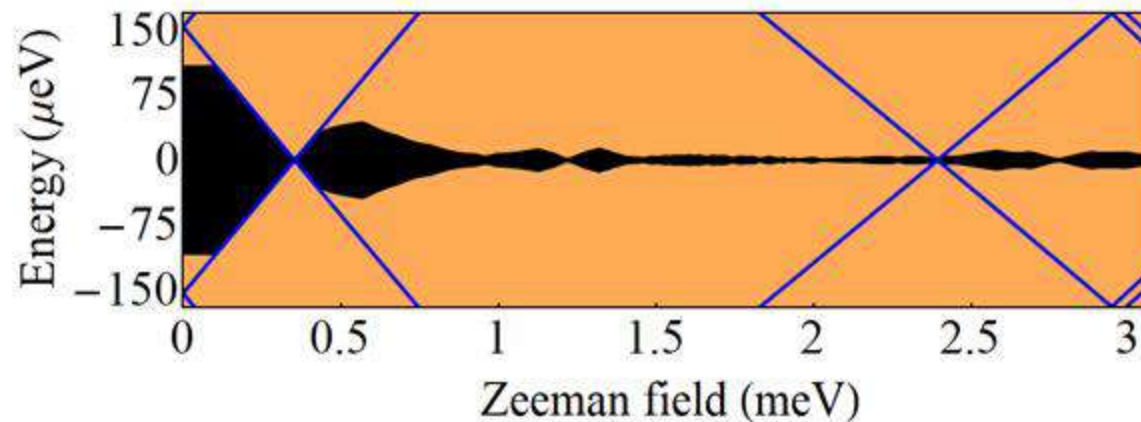
$$\Delta_0 = 0.25 \text{ meV}$$
$$\gamma = 0.75 \text{ meV}$$



DOS

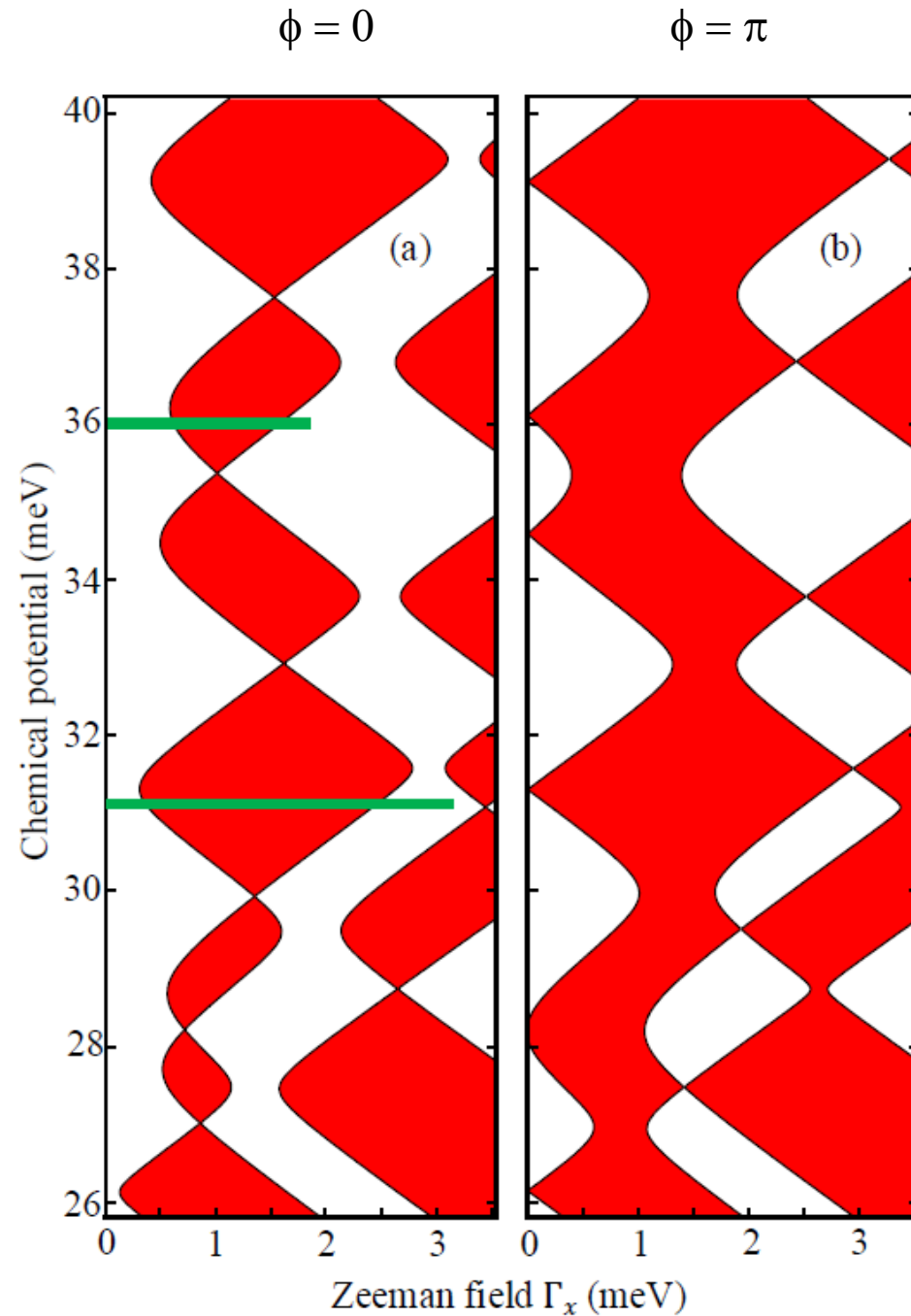


$A(\omega, k=0)$



$E_{\min}(\Gamma), E_{k=0}(\Gamma)$

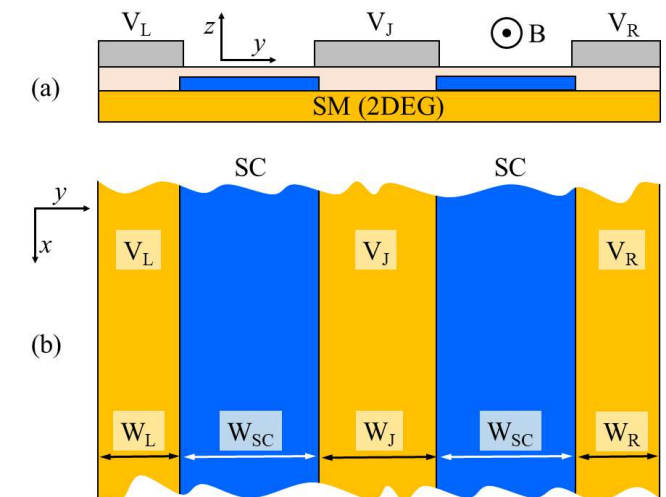
# Typical topological phase diagram



$$W_{SC} = 150 \text{ nm.}$$

$$V_J = 25 \text{ meV}$$

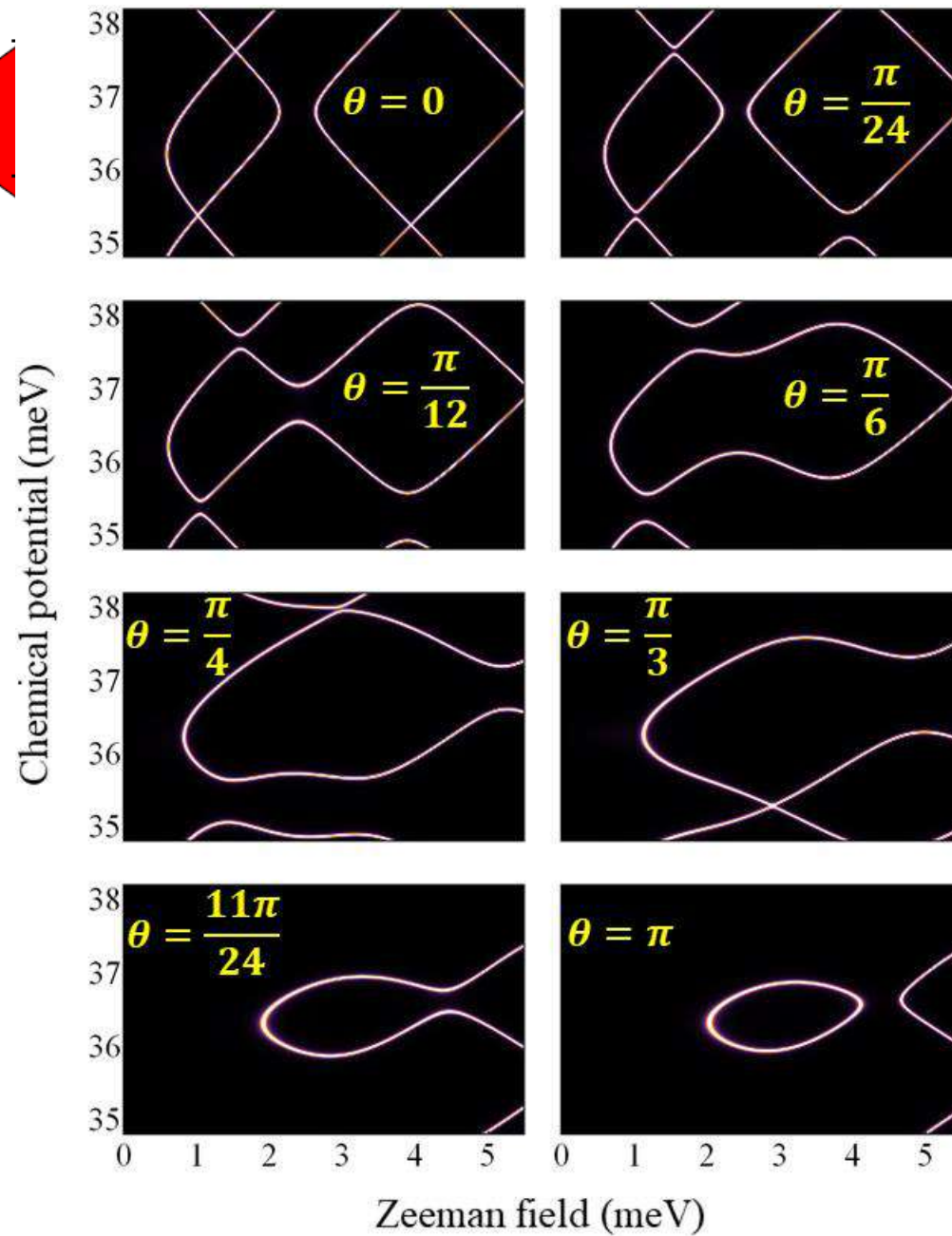
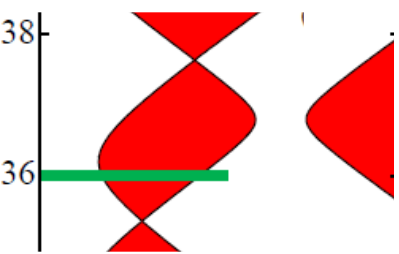
$$V_L = V_R = 100 \text{ meV}$$





# Effect of rotating the Zeeman field

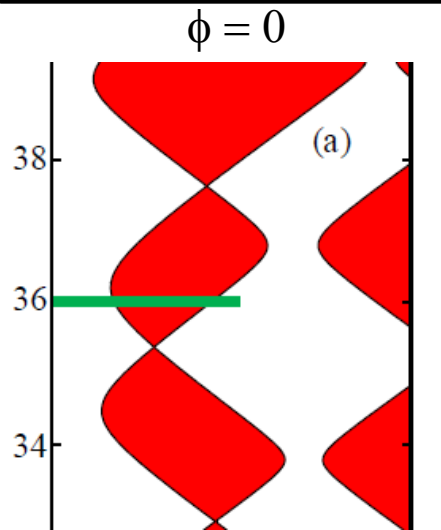
$$\phi = 0$$



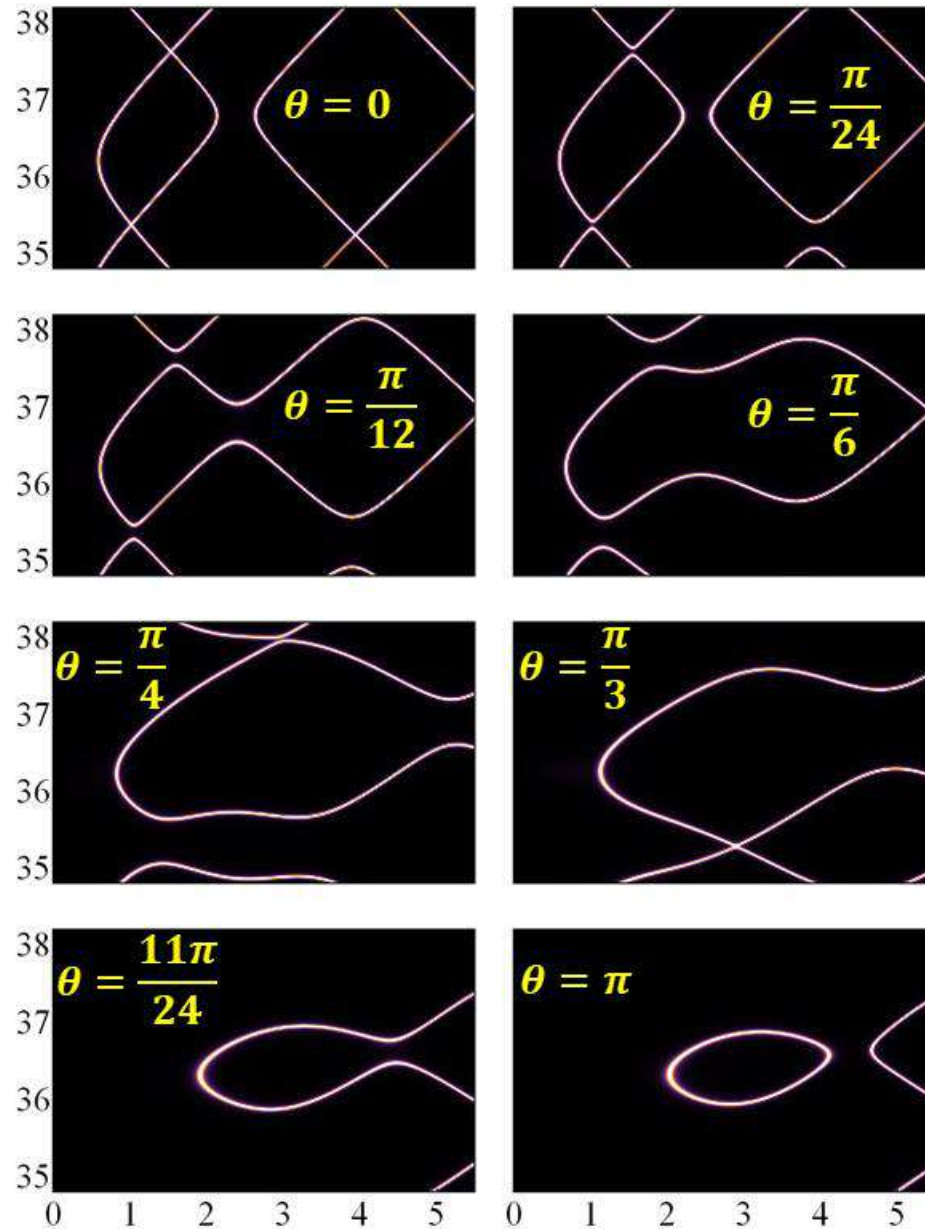
$$\Gamma_x = \Gamma \cos \theta$$

$$\Gamma_y = \Gamma \sin \theta.$$

# Effect of rotating the Zeeman field



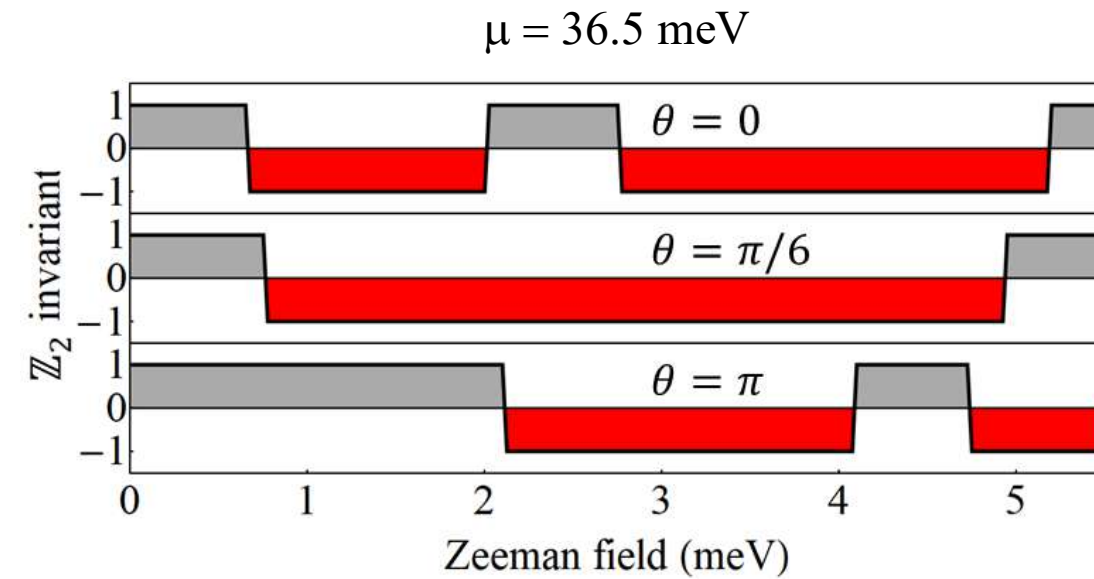
Chemical potential (meV)



Zeeman field (meV)

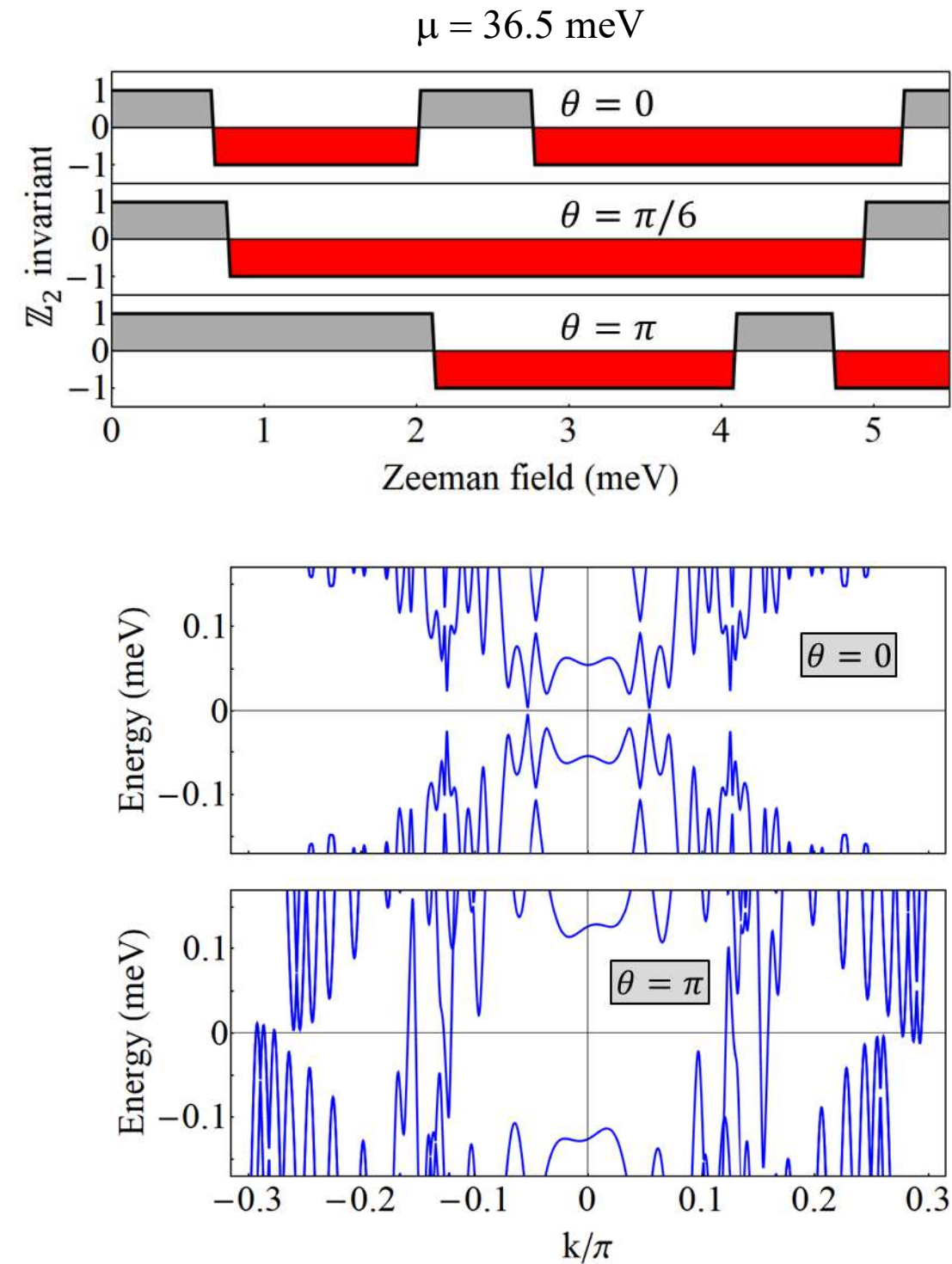
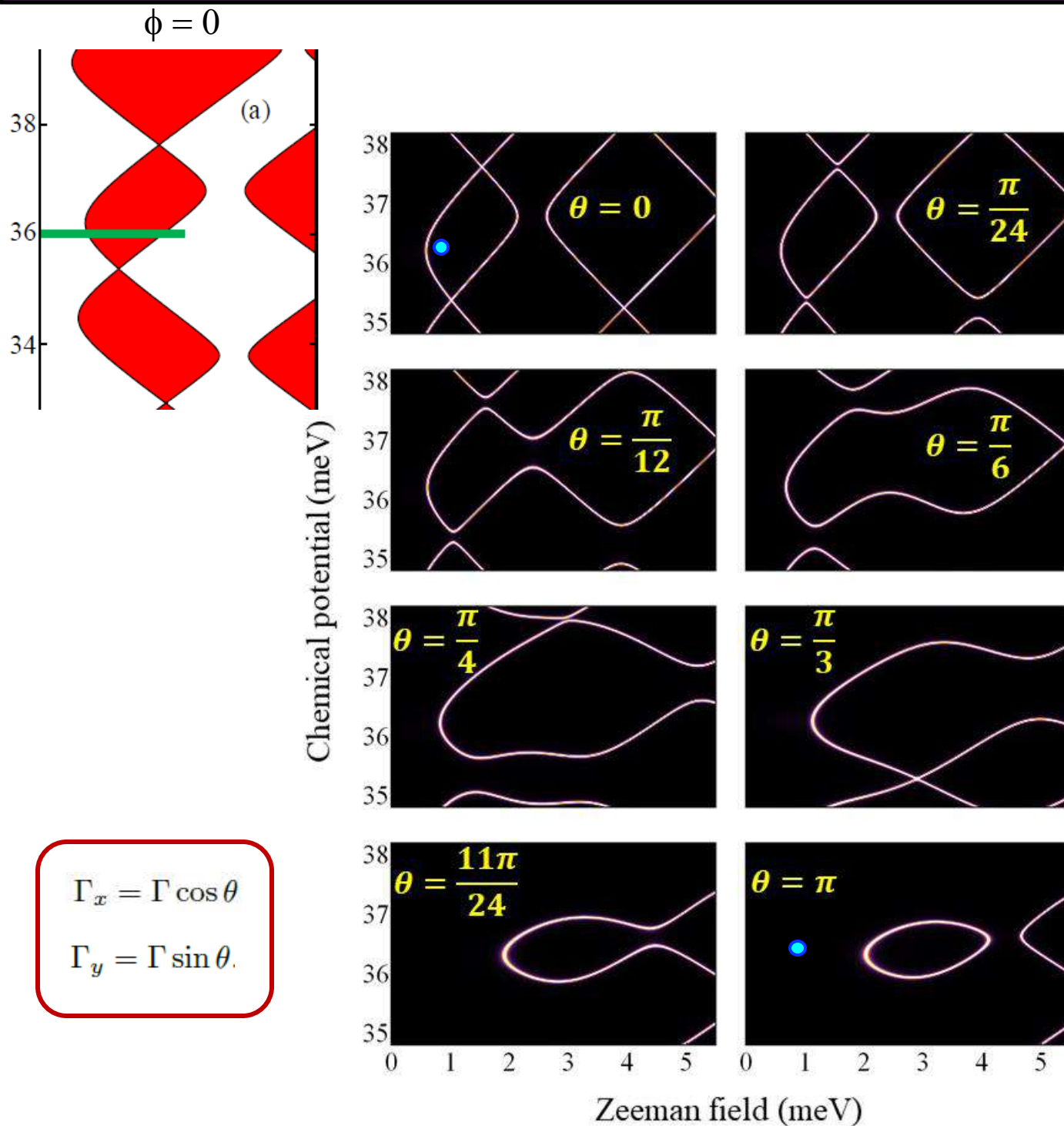
$$\Gamma_x = \Gamma \cos \theta$$

$$\Gamma_y = \Gamma \sin \theta.$$





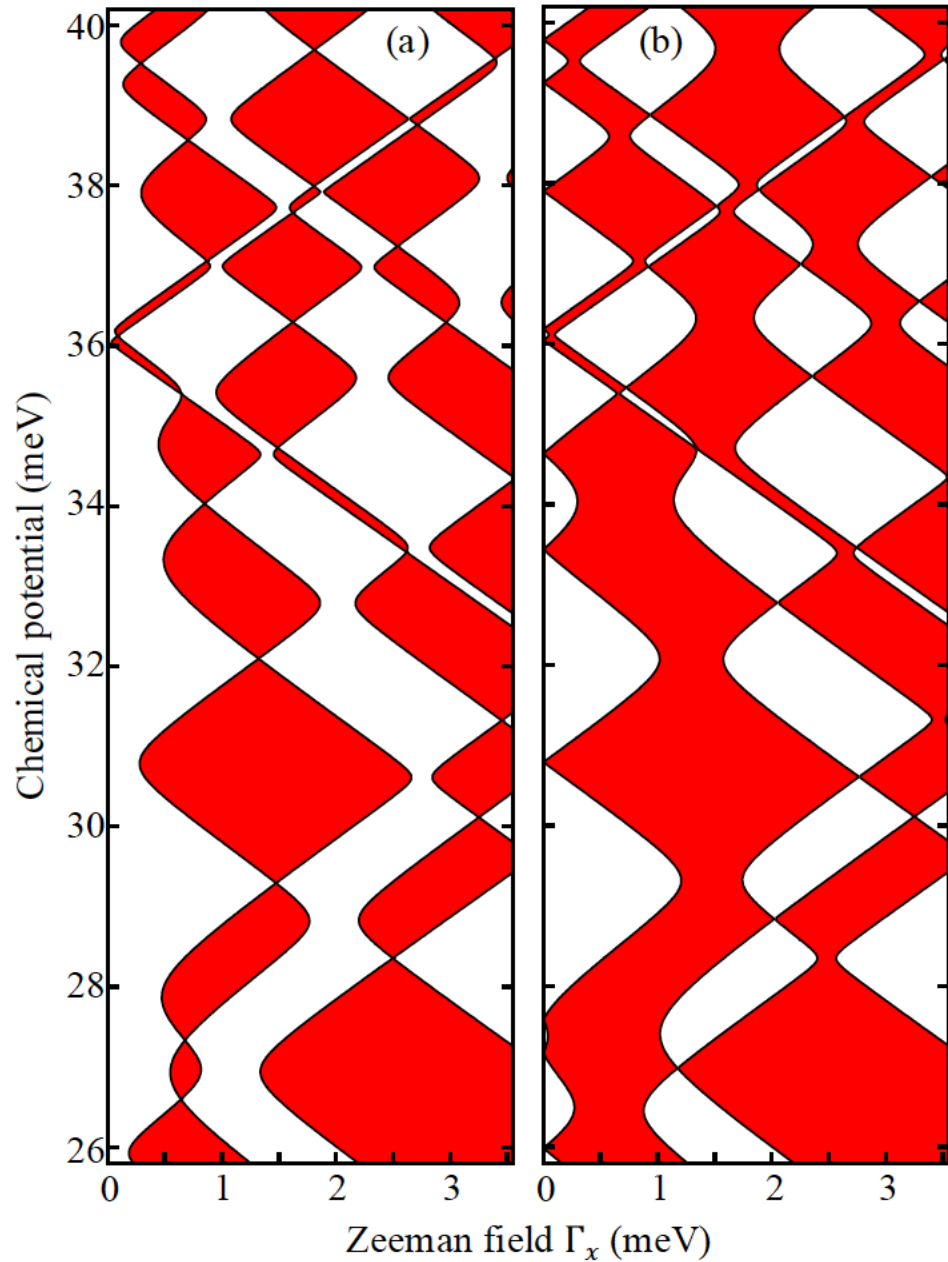
# Effect of rotating the Zeeman field



# Structures with undepleted outside SM regions

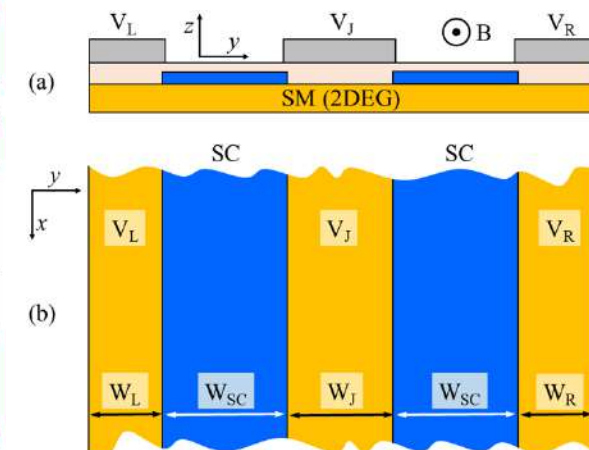
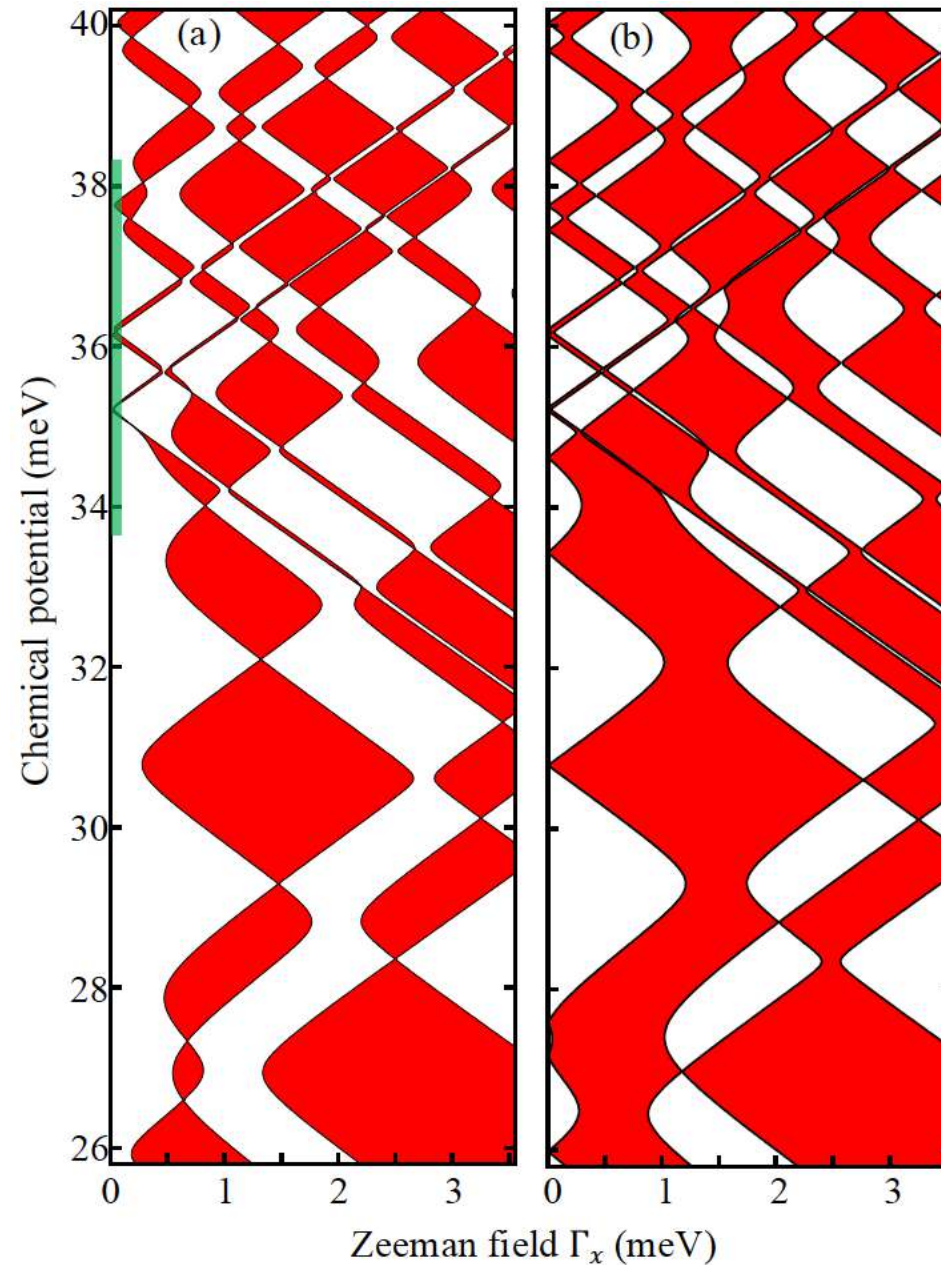
$$W_L = W_R = 100 \text{ nm}$$

$$V_L = V_R = 35 \text{ meV}$$

 $\phi = 0$ 
 $\phi = \pi$ 


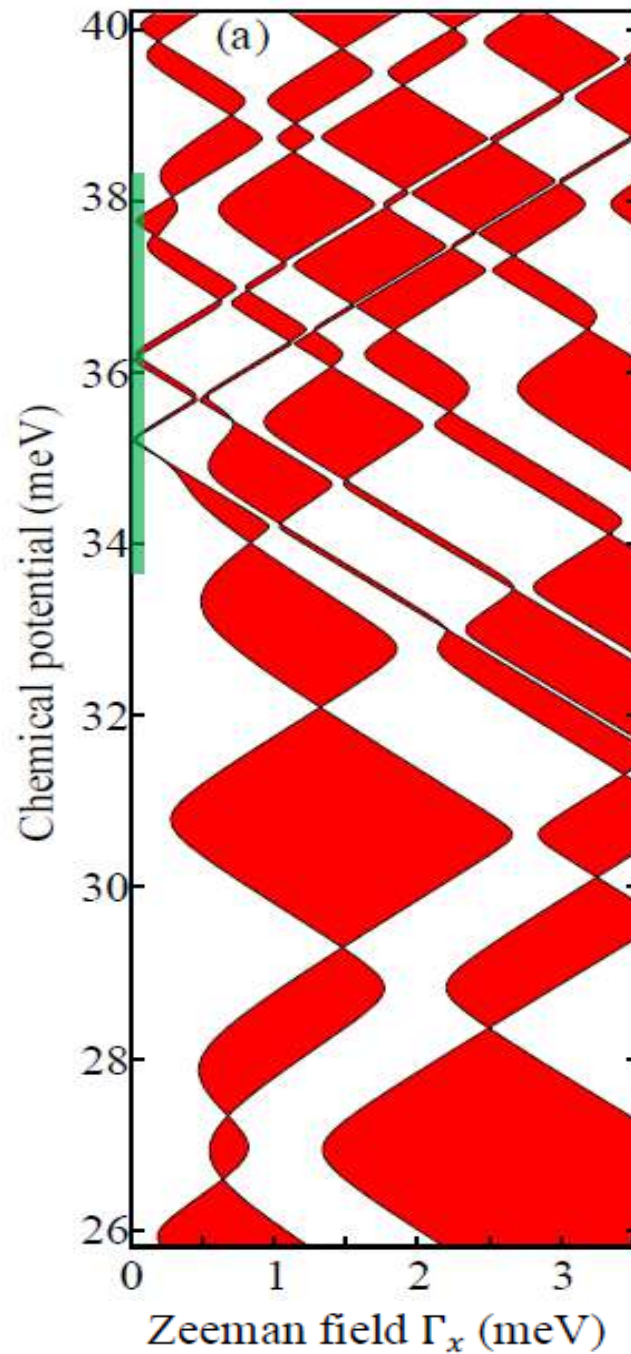
$$W_L = W_R = 195 \text{ nm}$$

$$V_L = V_R = 35 \text{ meV}$$

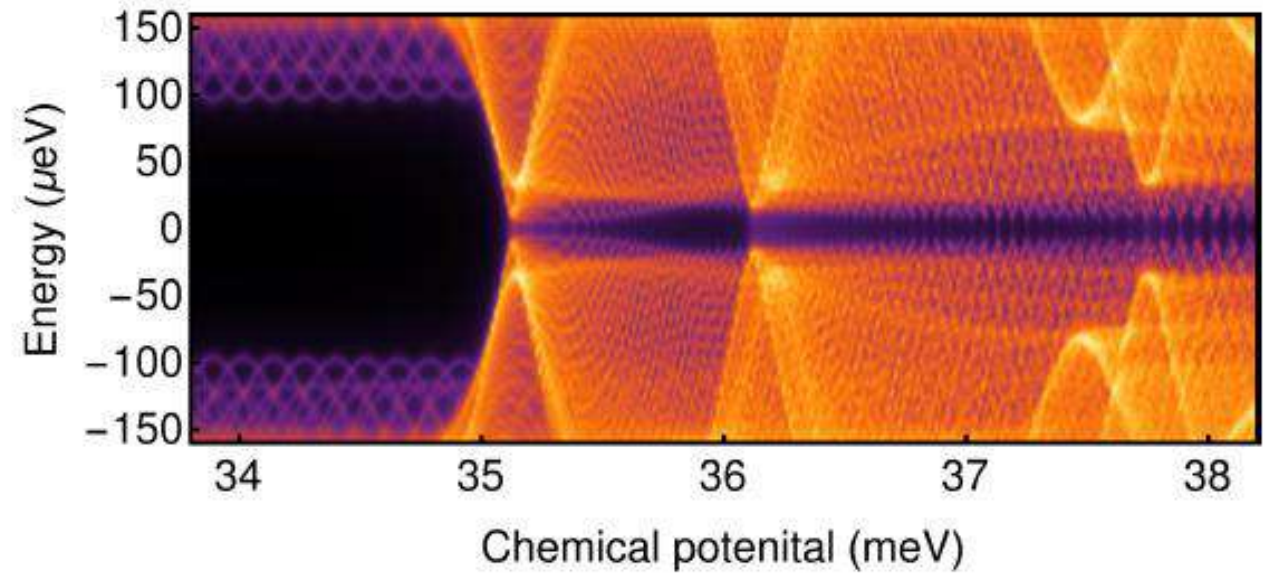
 $\phi = 0$ 
 $\phi = \pi$ 




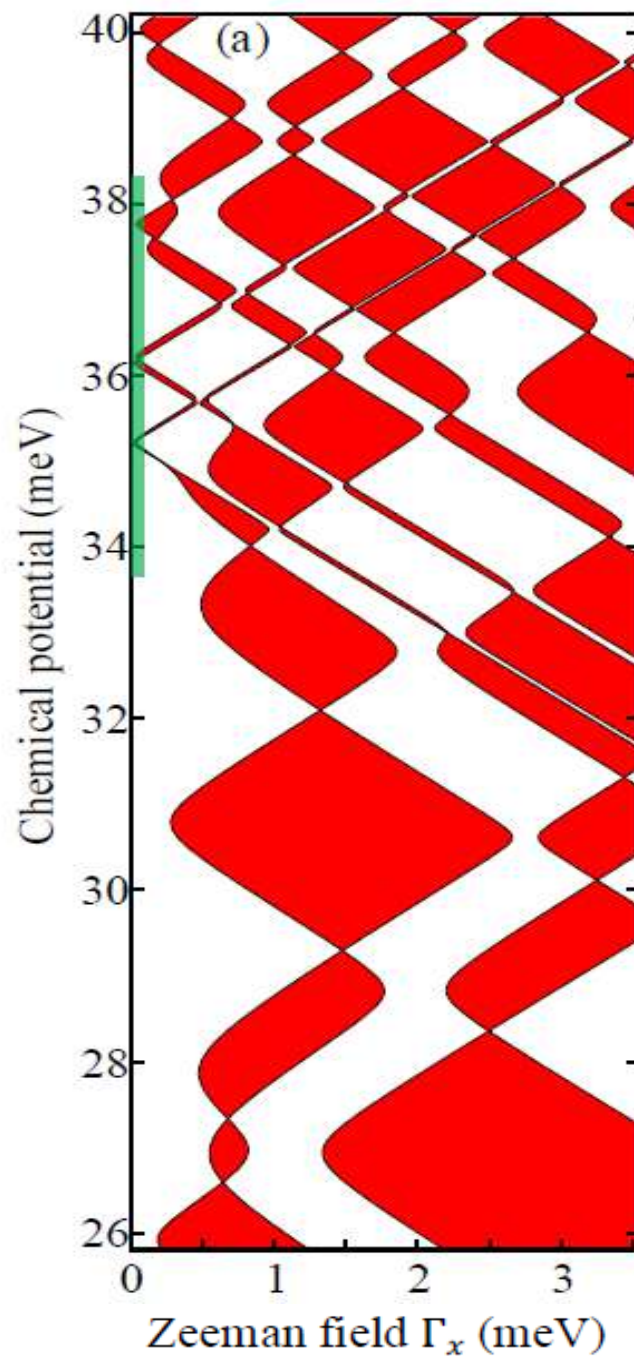
# Undepleted external SM regions



$$W_L = W_R = 195 \text{ nm}$$
$$V_L = V_R = 35 \text{ meV}$$

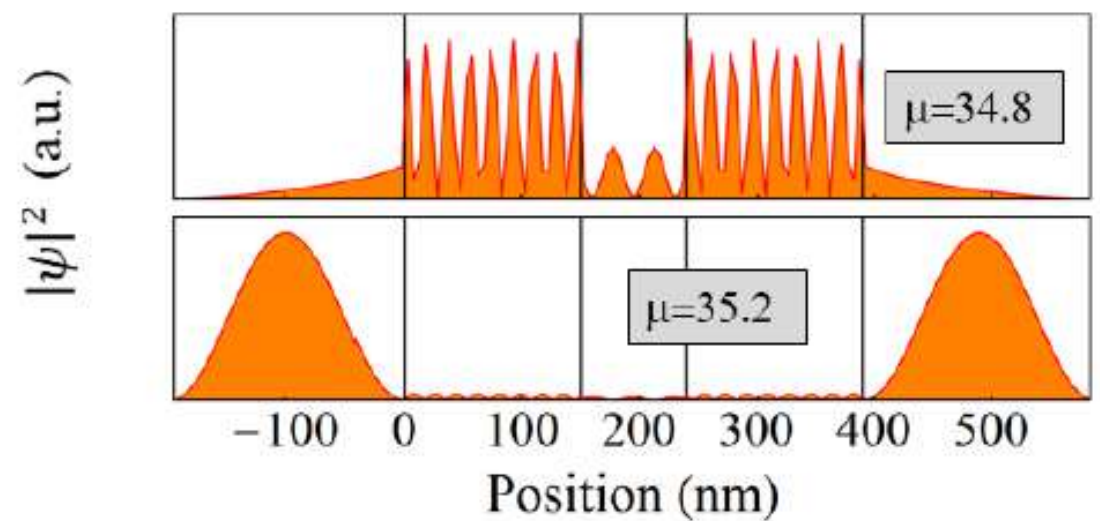
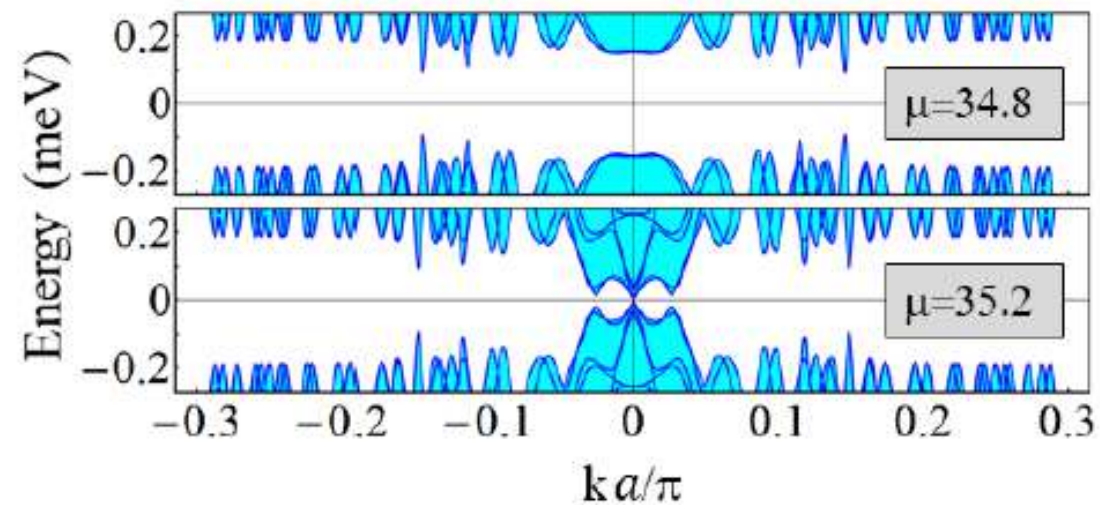


# Undepleted external SM regions



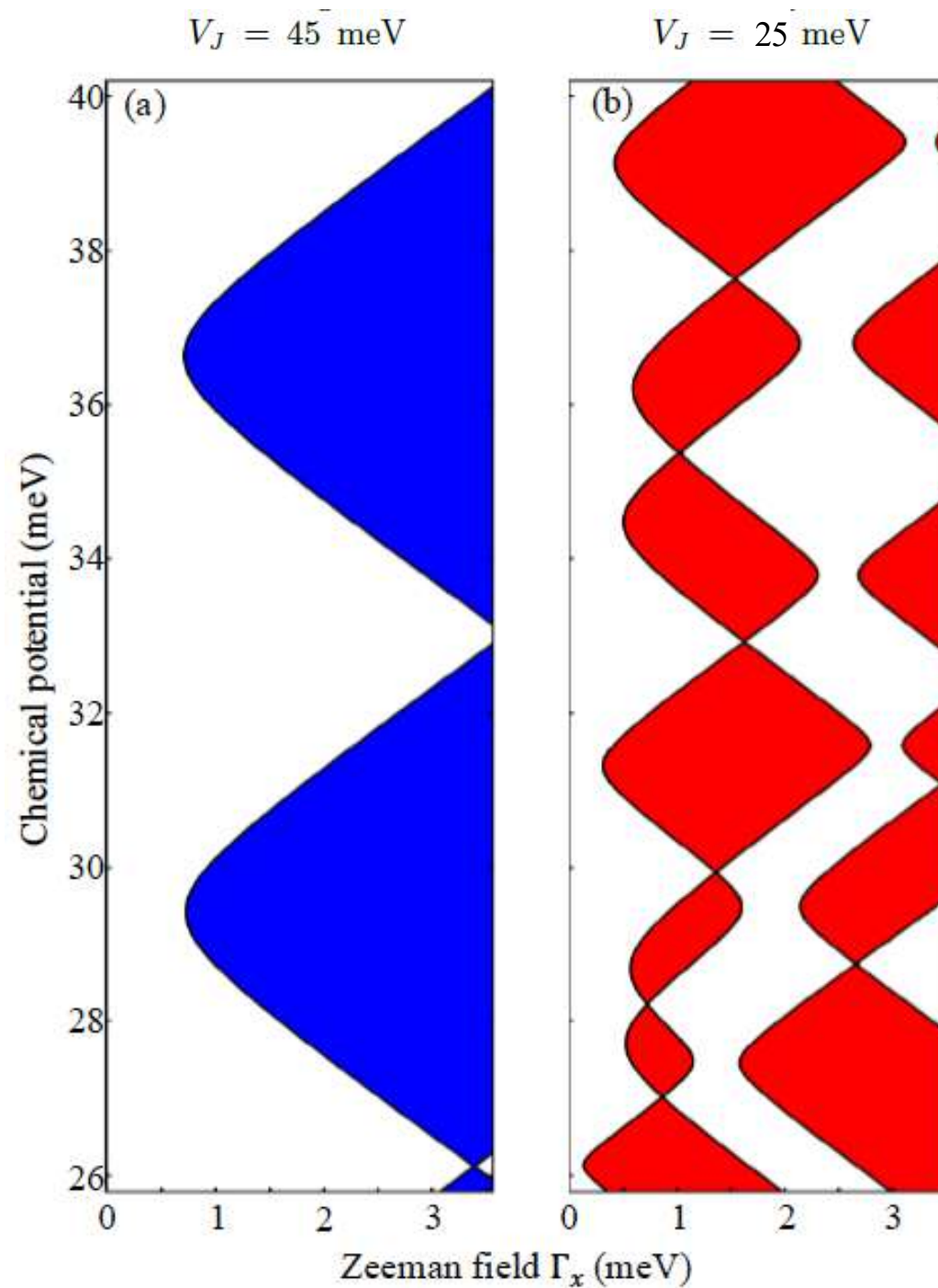
$$W_L = W_R = 195 \text{ nm}$$

$$V_L = V_R = 35 \text{ meV}$$



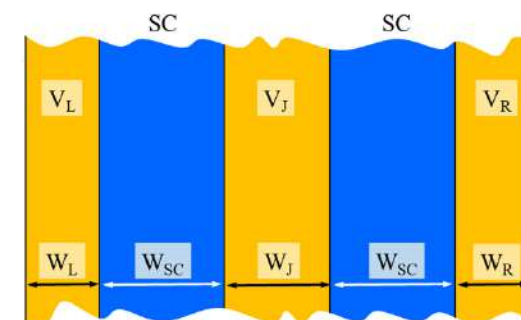
$k=0$

# Depleted junction region & the wire-JJ crossover



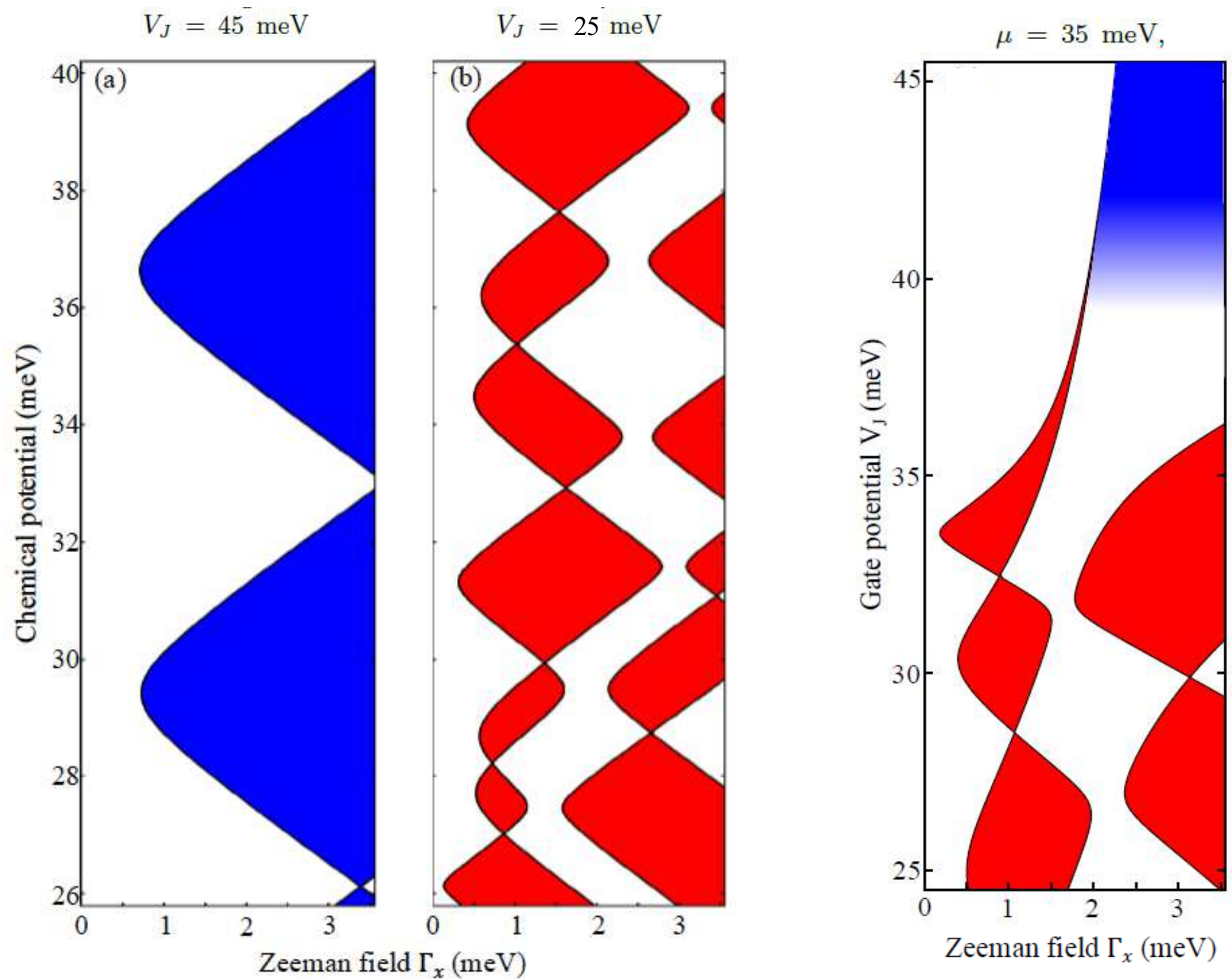
$$W_{SC} = 150 \text{ nm.}$$

$$V_L = V_R = 100 \text{ meV.}$$



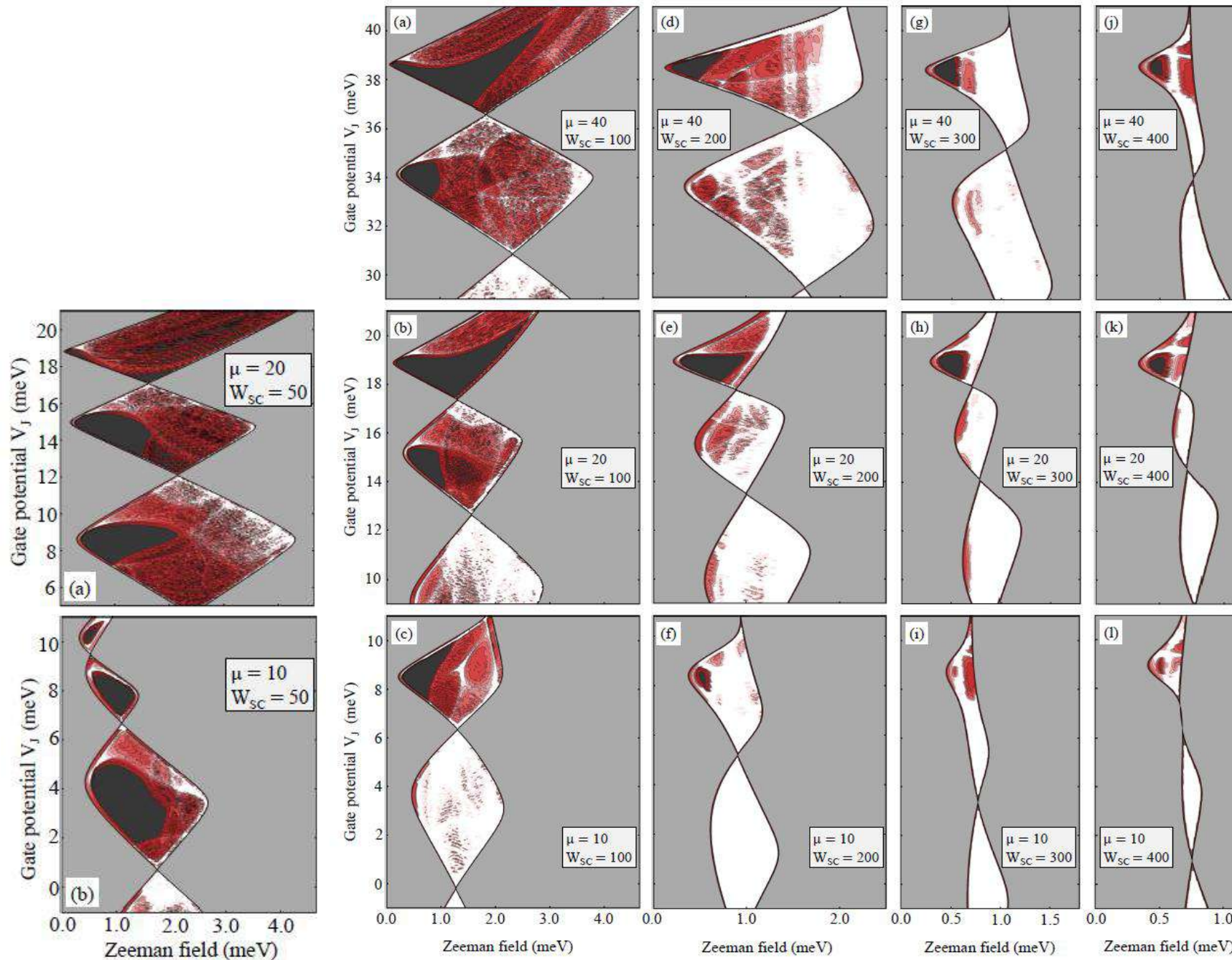


# Depleted junction region & the wire-JJ crossover



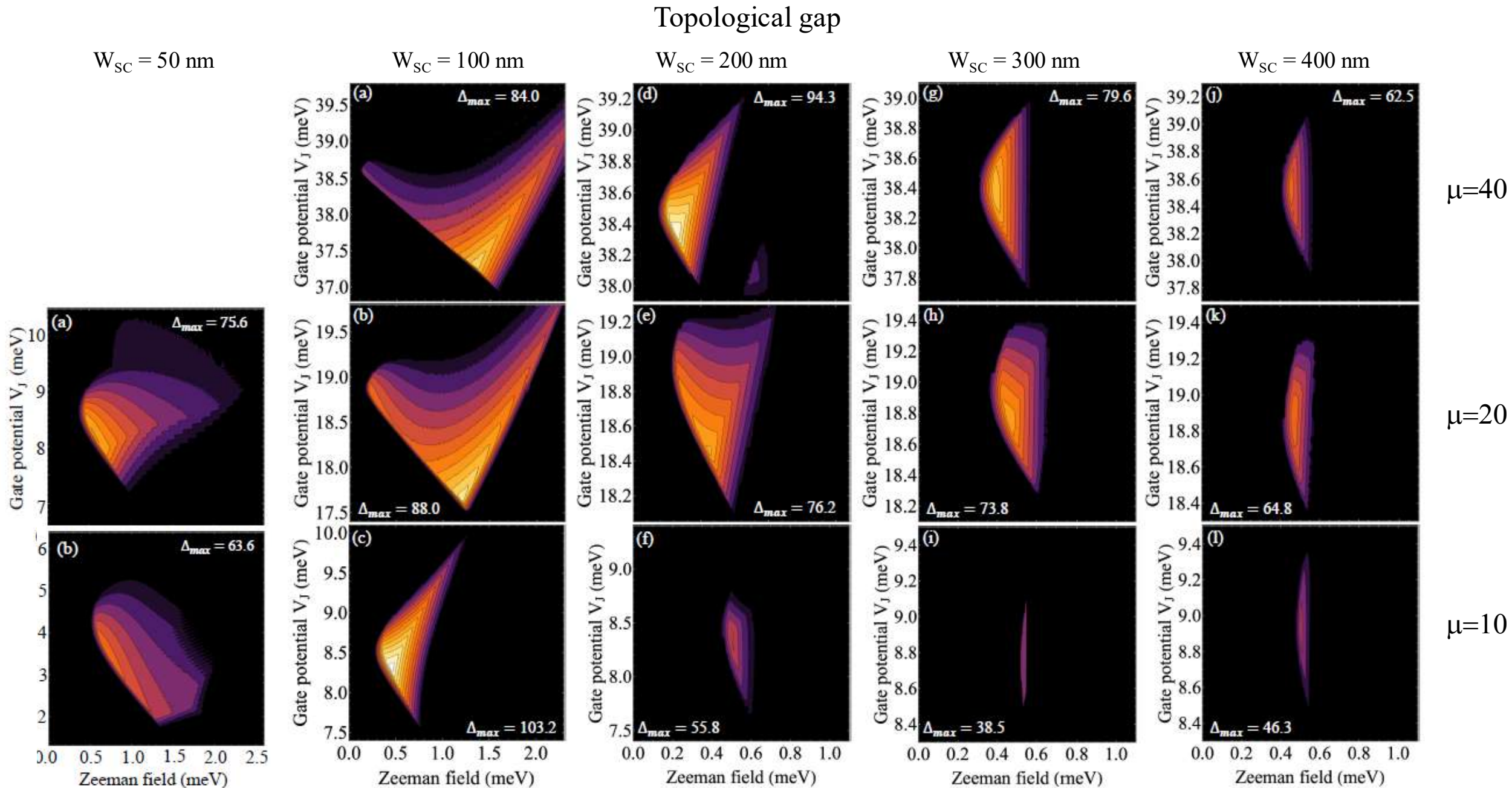


# Dependence of the topological gap on the width of the SC films



DOS at  $E = 35 \mu\text{eV}$   
( $\phi=0$ )

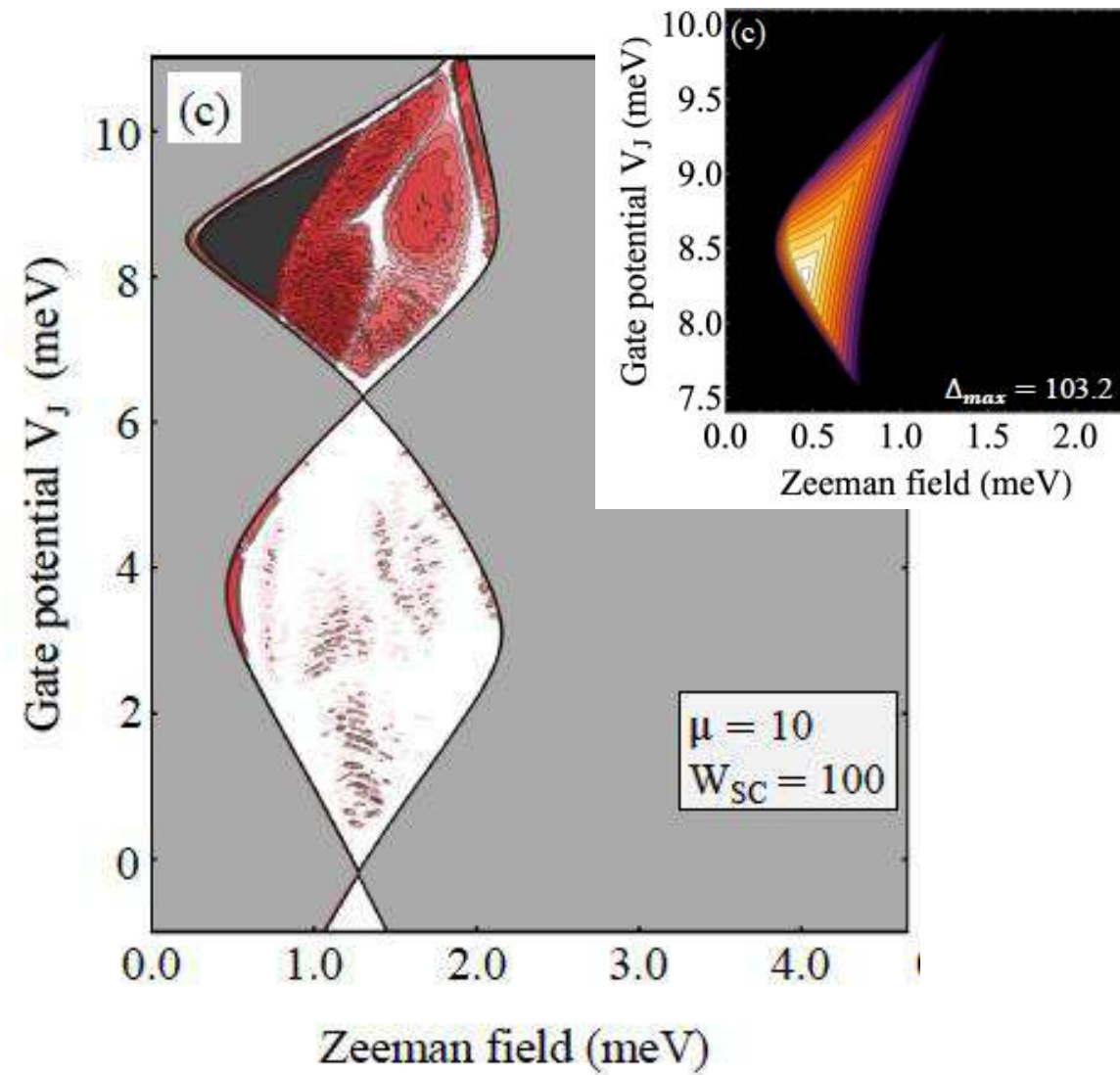
# Dependence of the topological gap on the width of the SC films



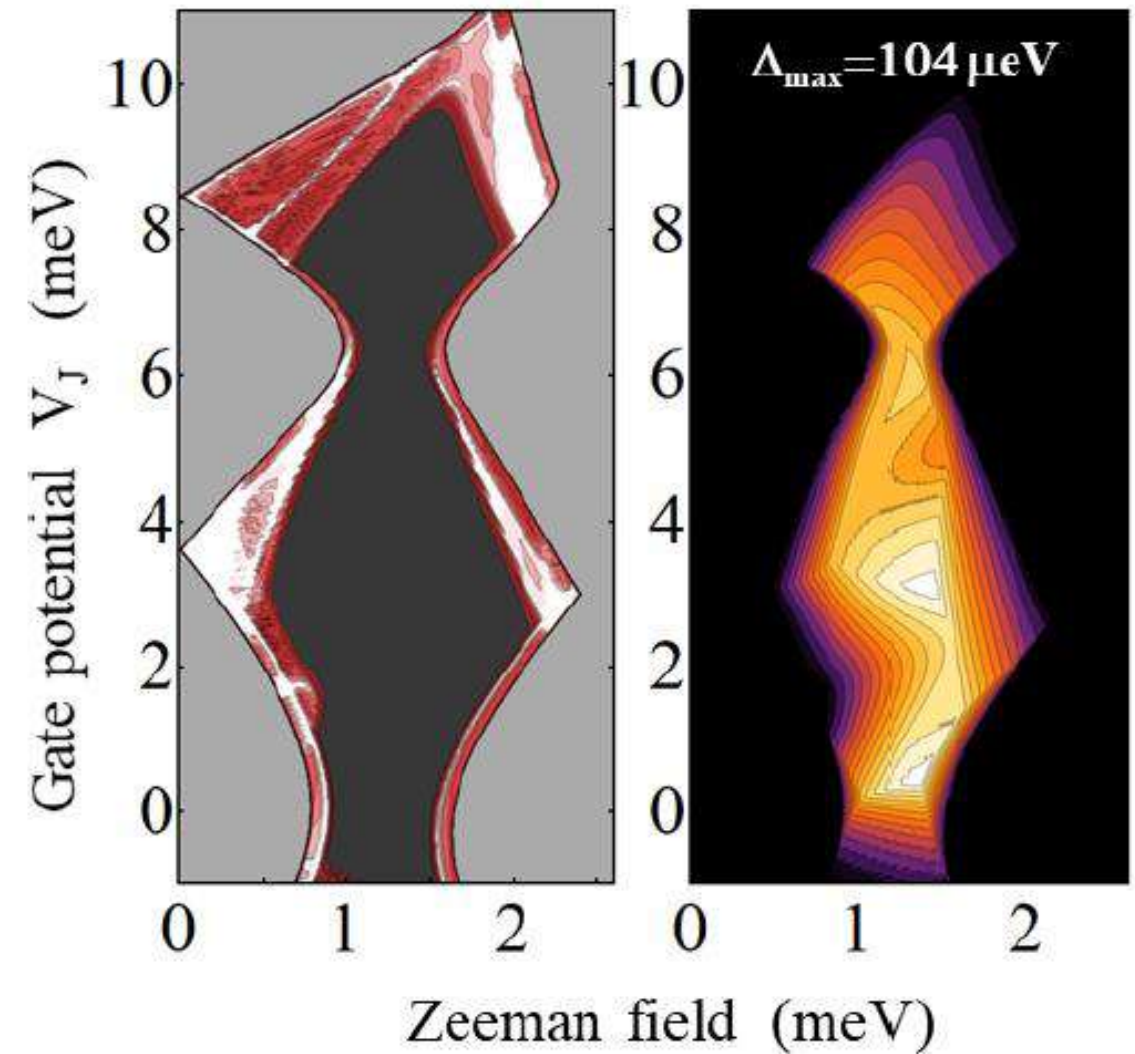


# JJ structure with phase difference $\phi=\pi$

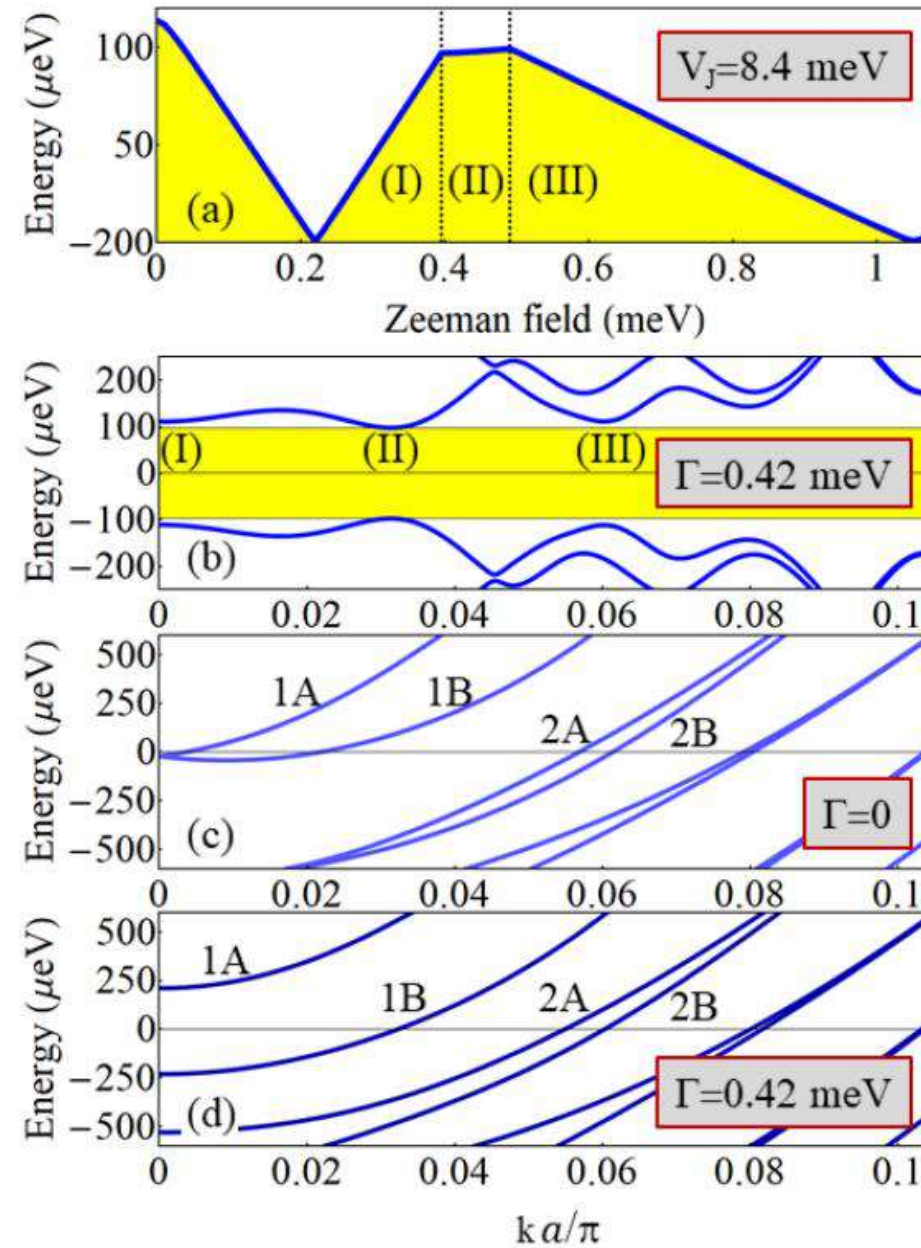
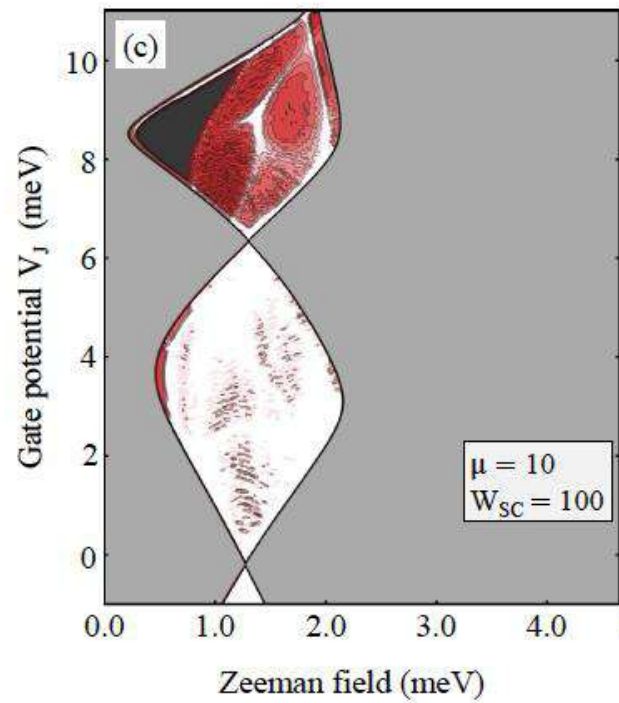
$\phi=0$



$\phi=\pi$

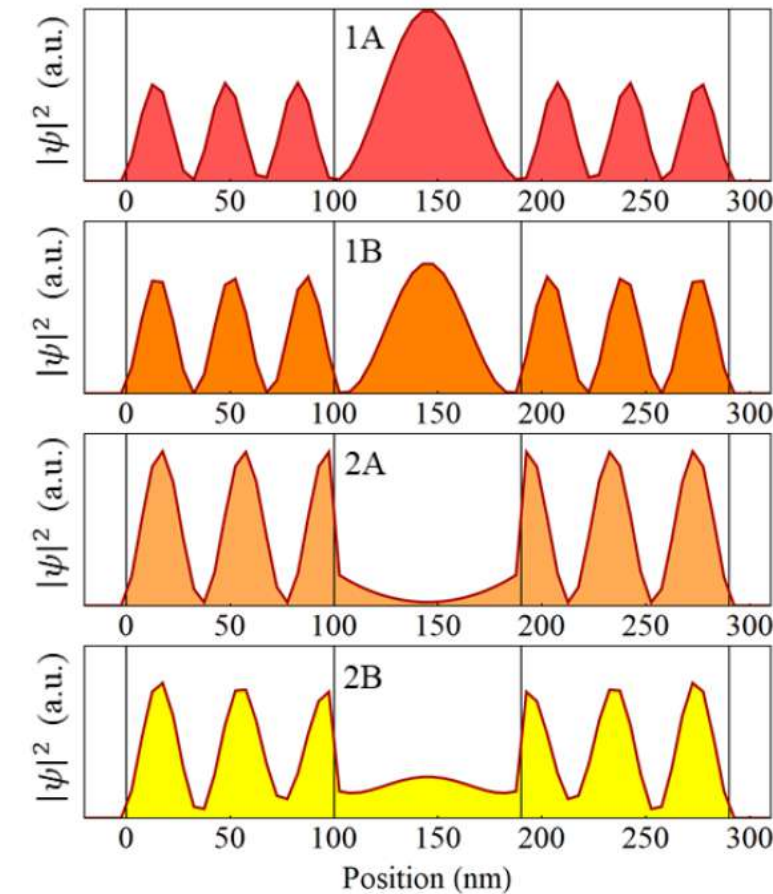
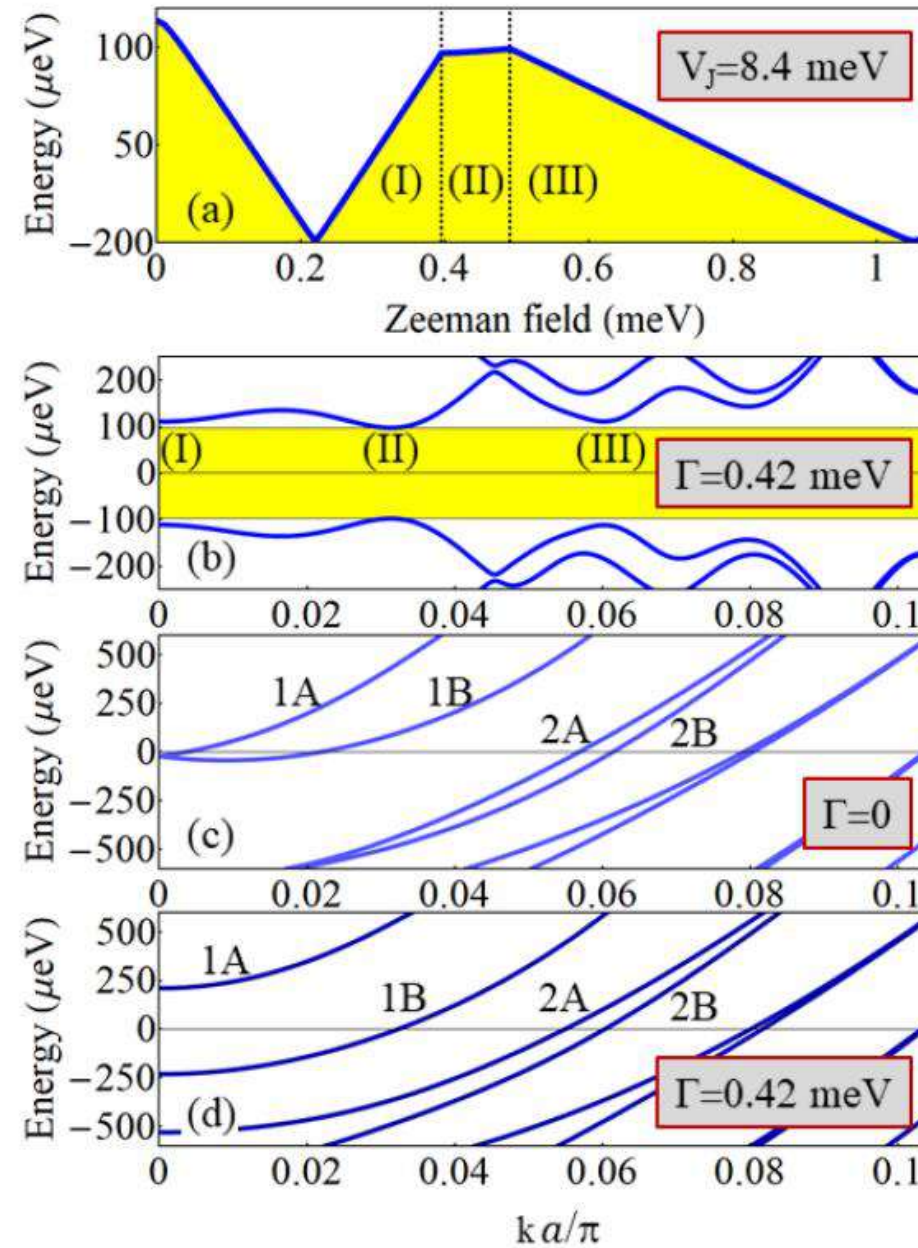
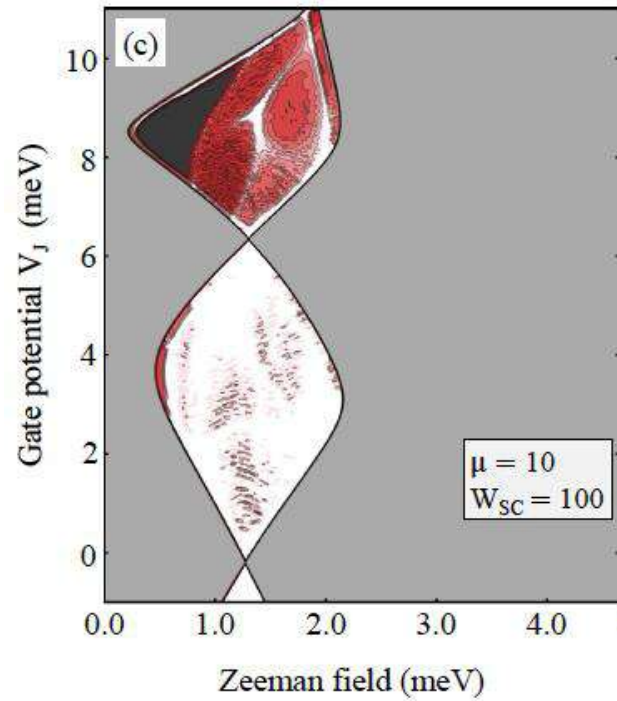


# Modes that control the quasiparticle gap



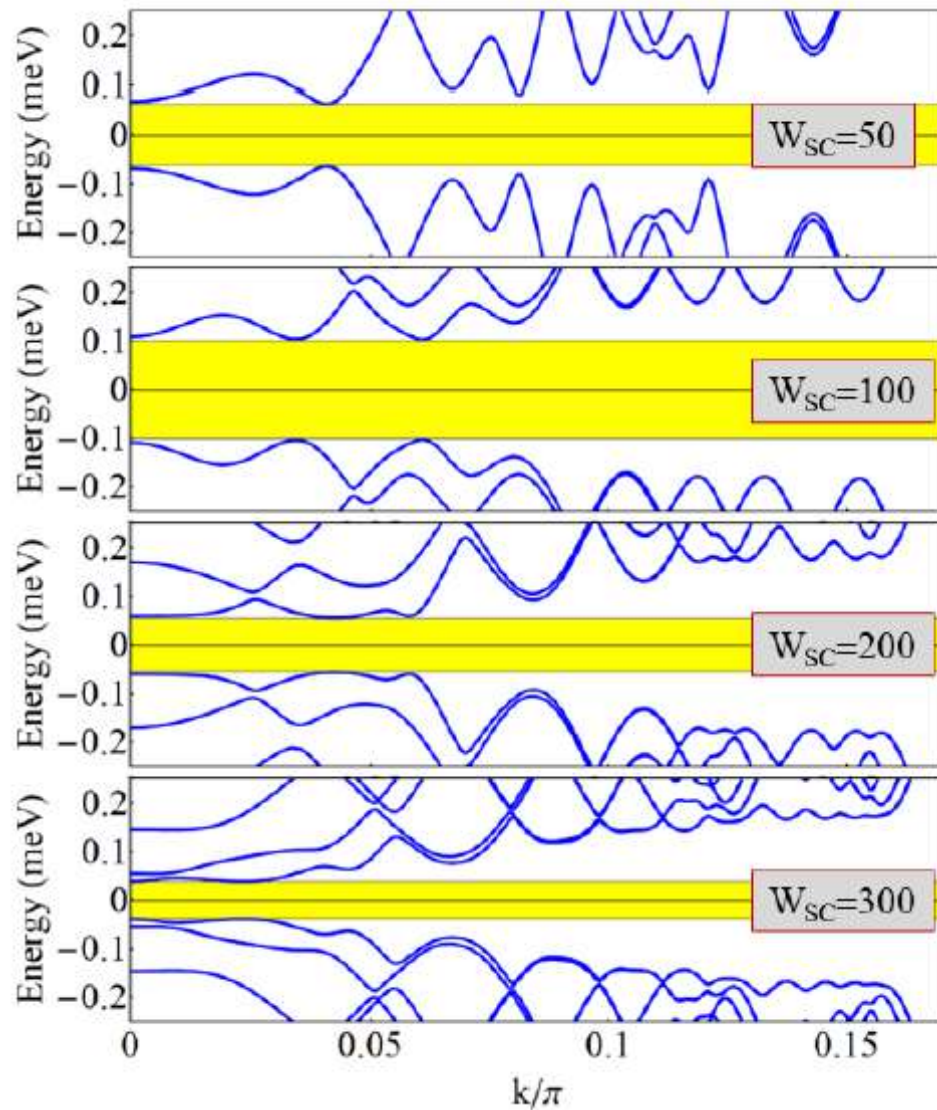


# Modes that control the quasiparticle gap

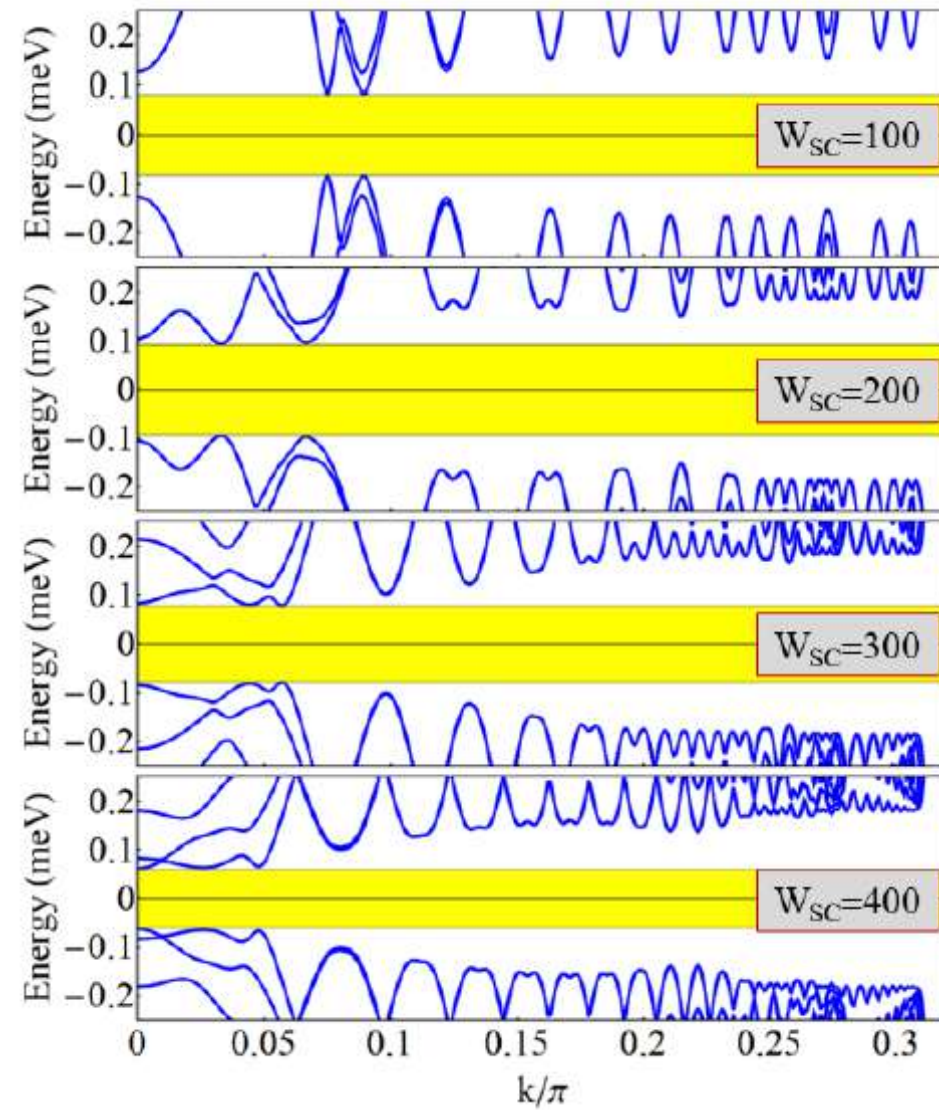


# Energy spectra near the maximum topological gap

$\mu=10$  meV

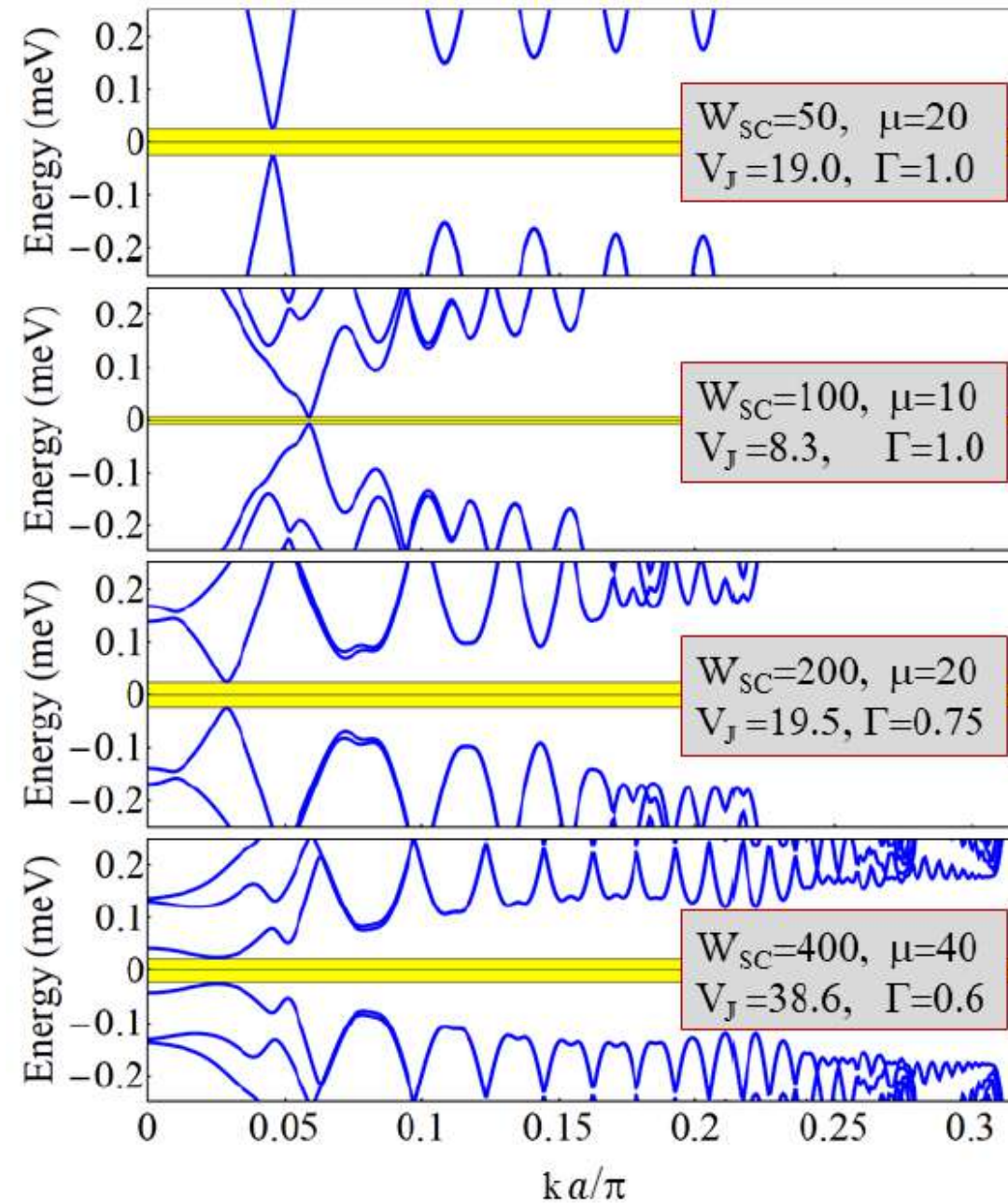


$\mu=40$  meV

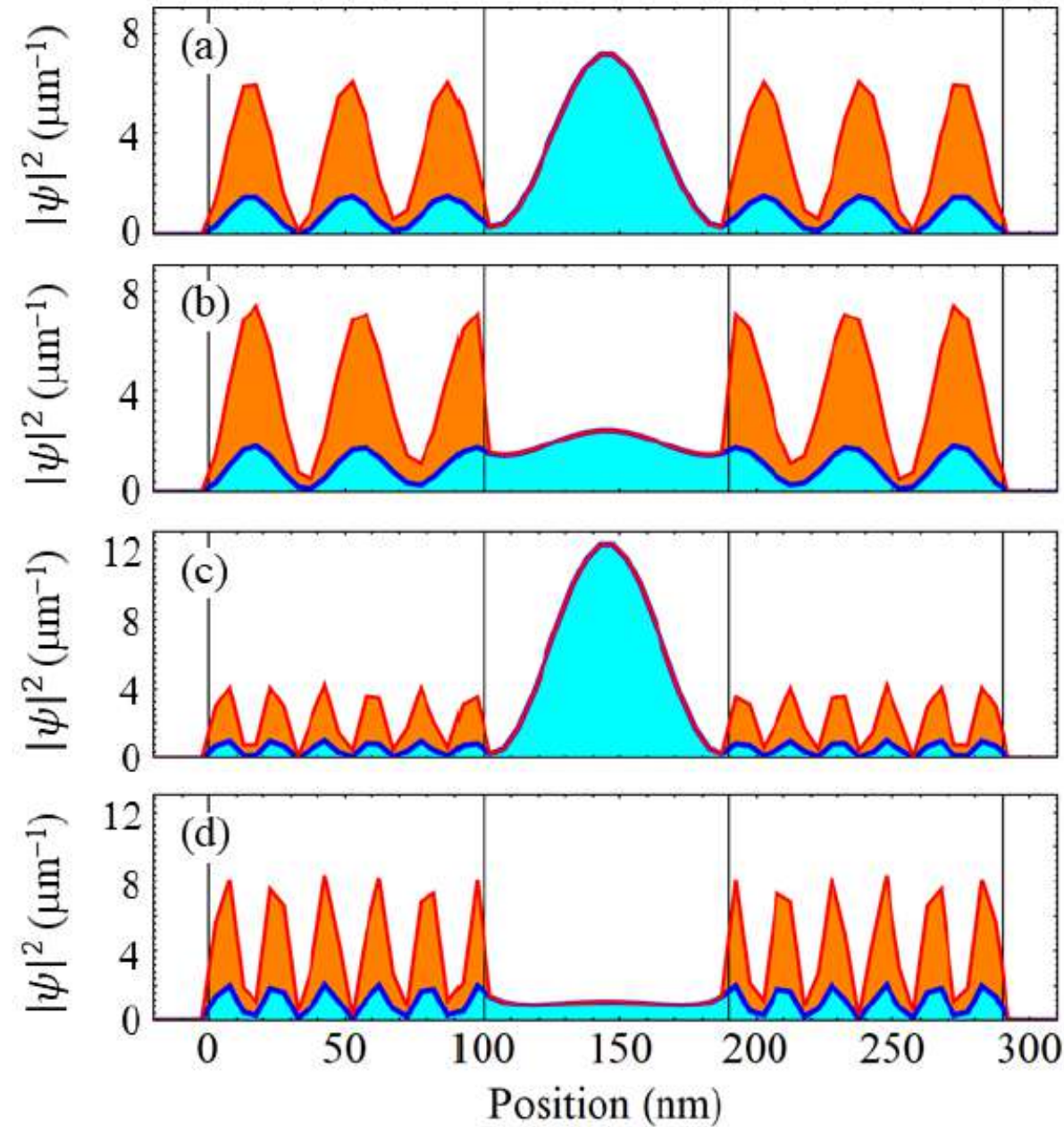
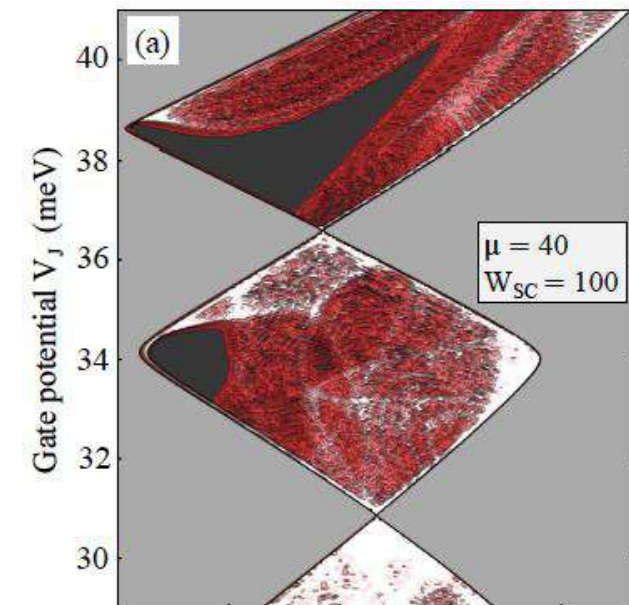
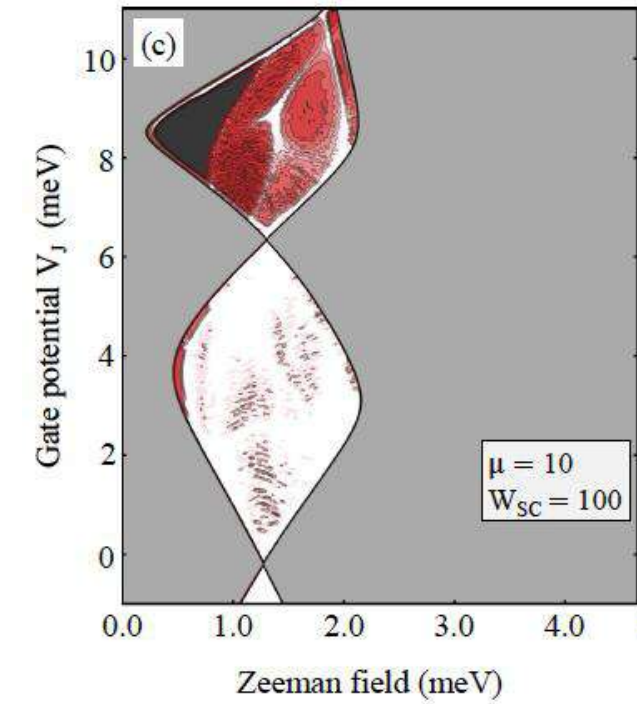




# Energy spectra with small topological gaps



# Gap-edge modes (near the maximum topological gap)



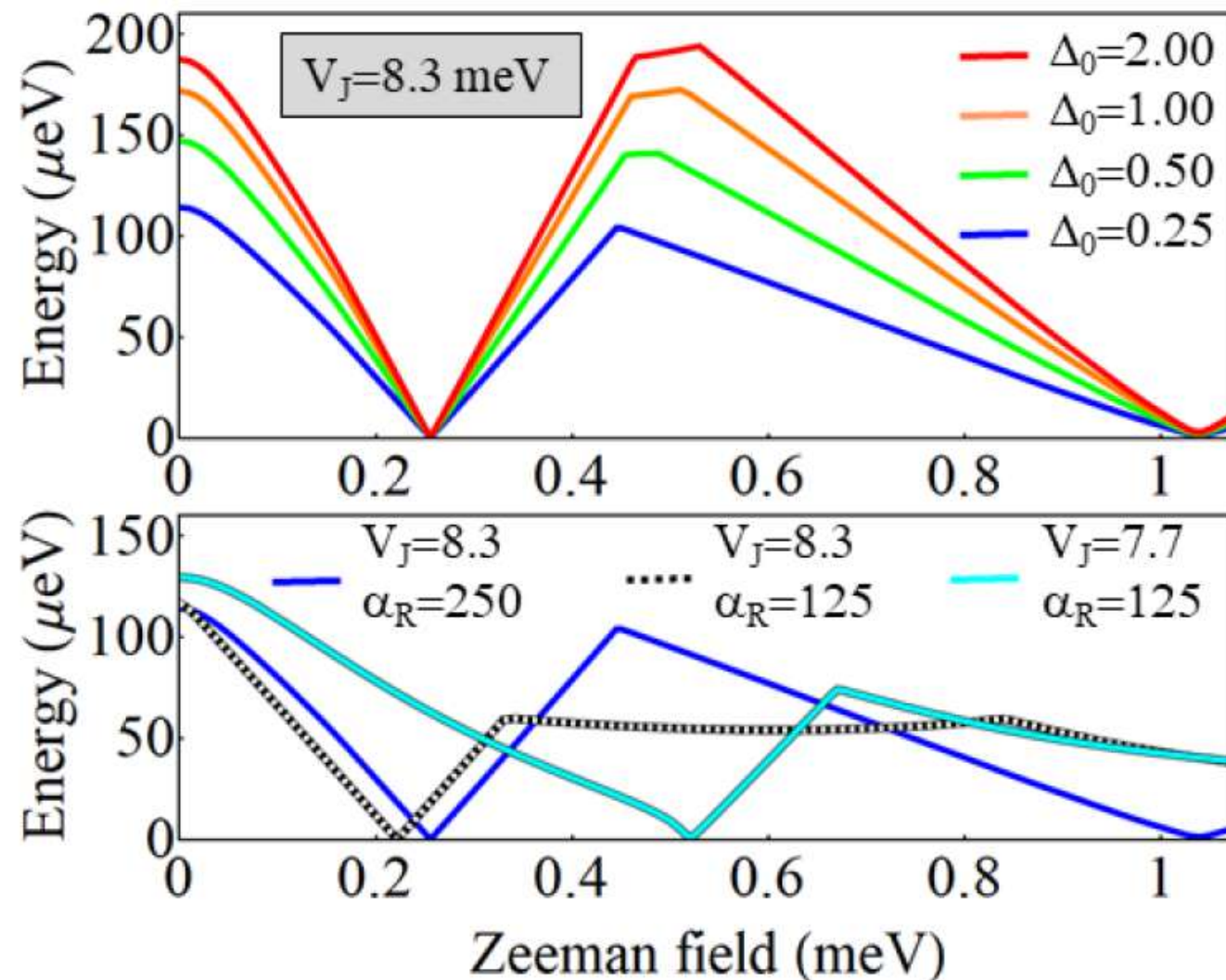
$\mu = 10$  meV

$\mu = 40$  meV

# Partial conclusion & future tasks

- In planar JJ devices, the topological gap has a nonmonotonic dependence on the width of the SC films, with an optimum width that depends on other system parameters (e.g.,  $\mu$ )
- Determine the dependence of the optimal regime on the parent SC gap and the SOC type & strength
- Investigate disorder effects in JJ structures with narrow superconductors
- Calculate the topological phase diagram (in the presence of disorder)

# Dependence of the qp gap on the parent SC gap & the Rashba SOC

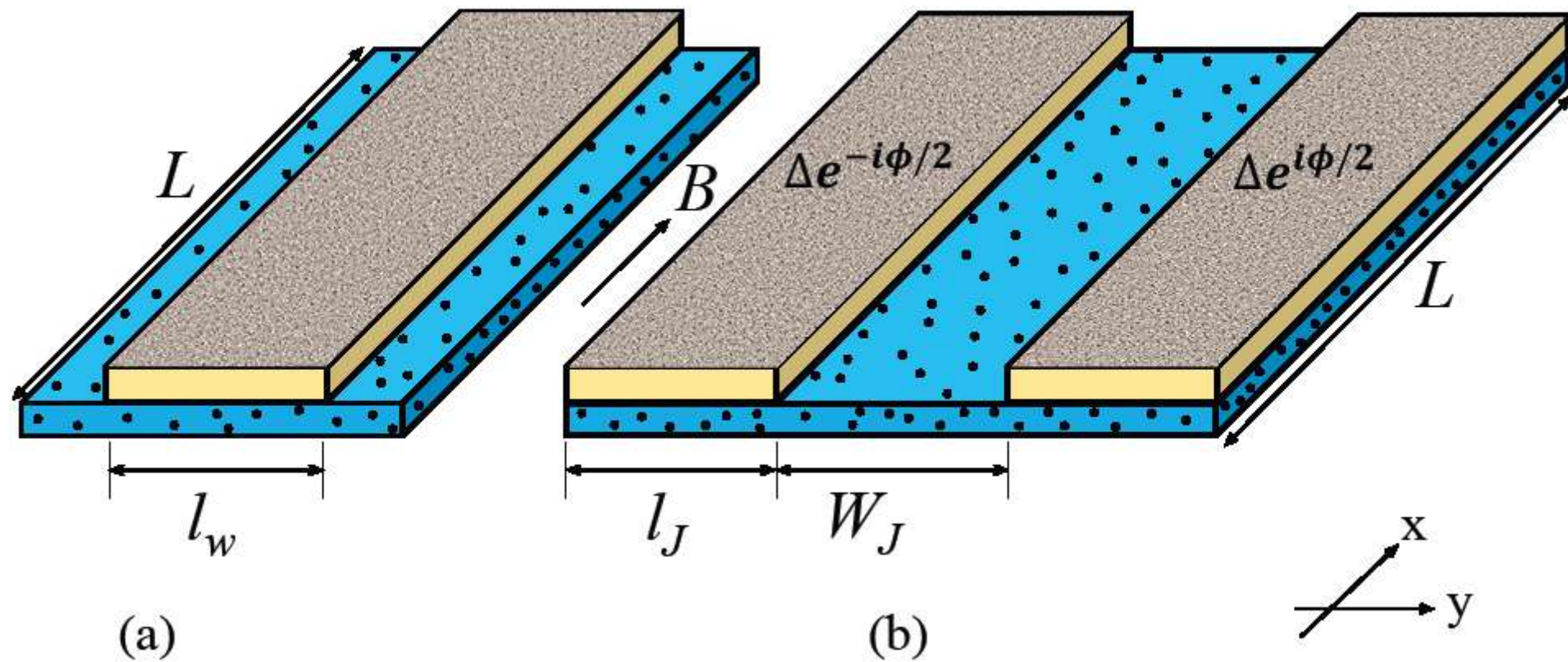


$\mu = 10 \text{ meV}$   
 $W_{\text{SC}} = 100 \text{ nm}$

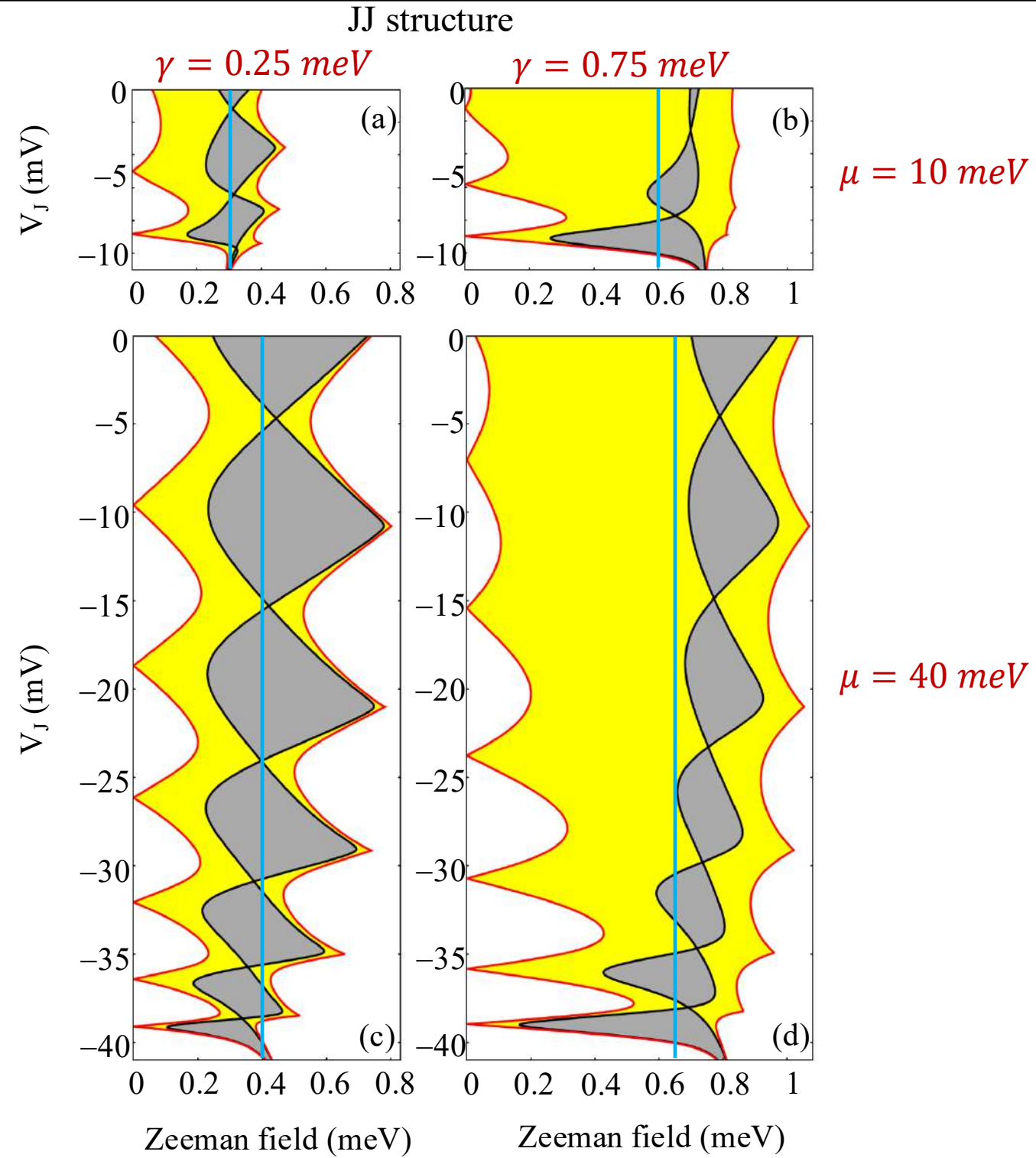
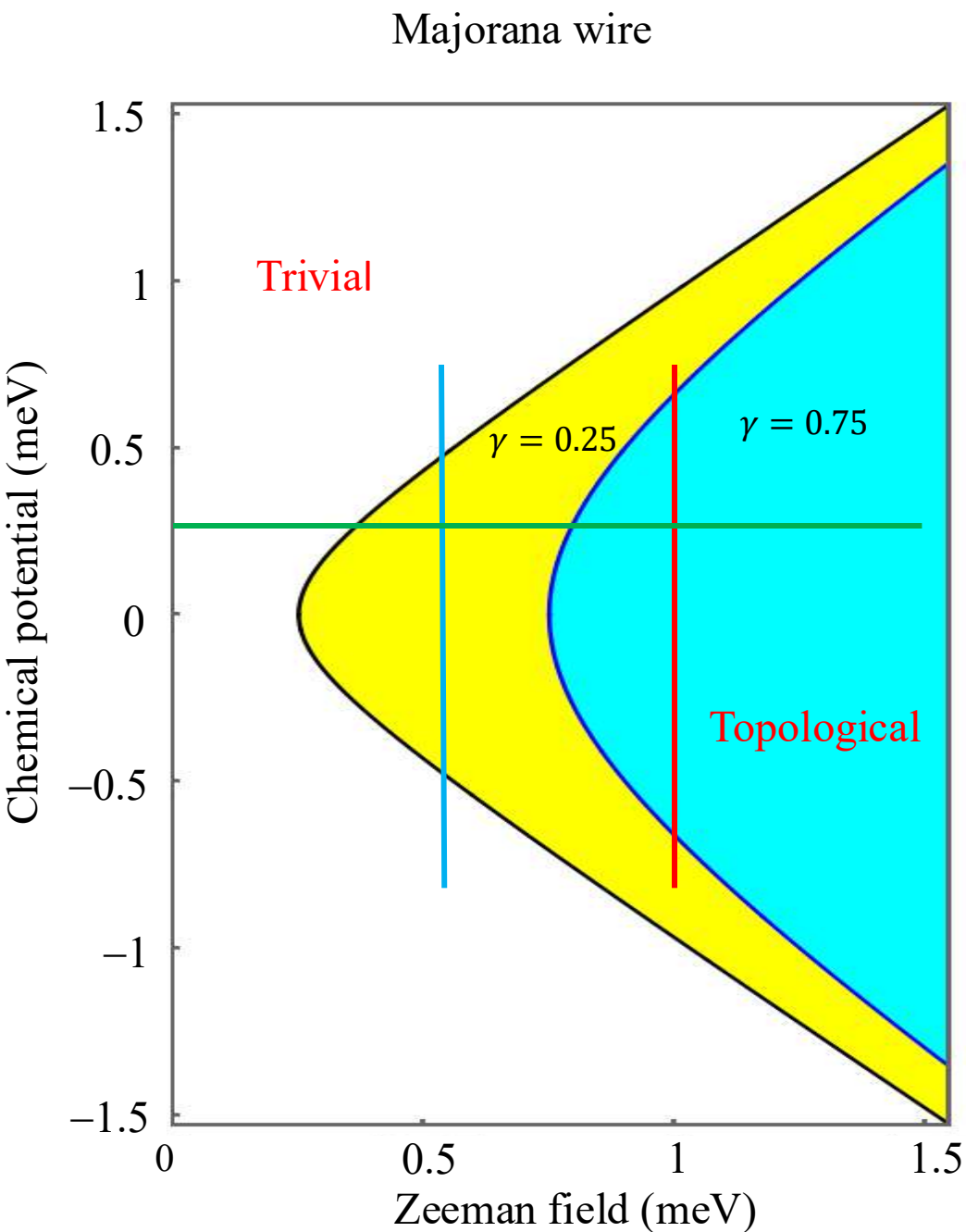


# Disorder effects: Majorana wires versus Josephson junctions

$$\begin{aligned}l_w &= 100 \text{ nm} \\l_J &= 800 \text{ nm} \\W_J &= 100 \text{ nm}\end{aligned}$$

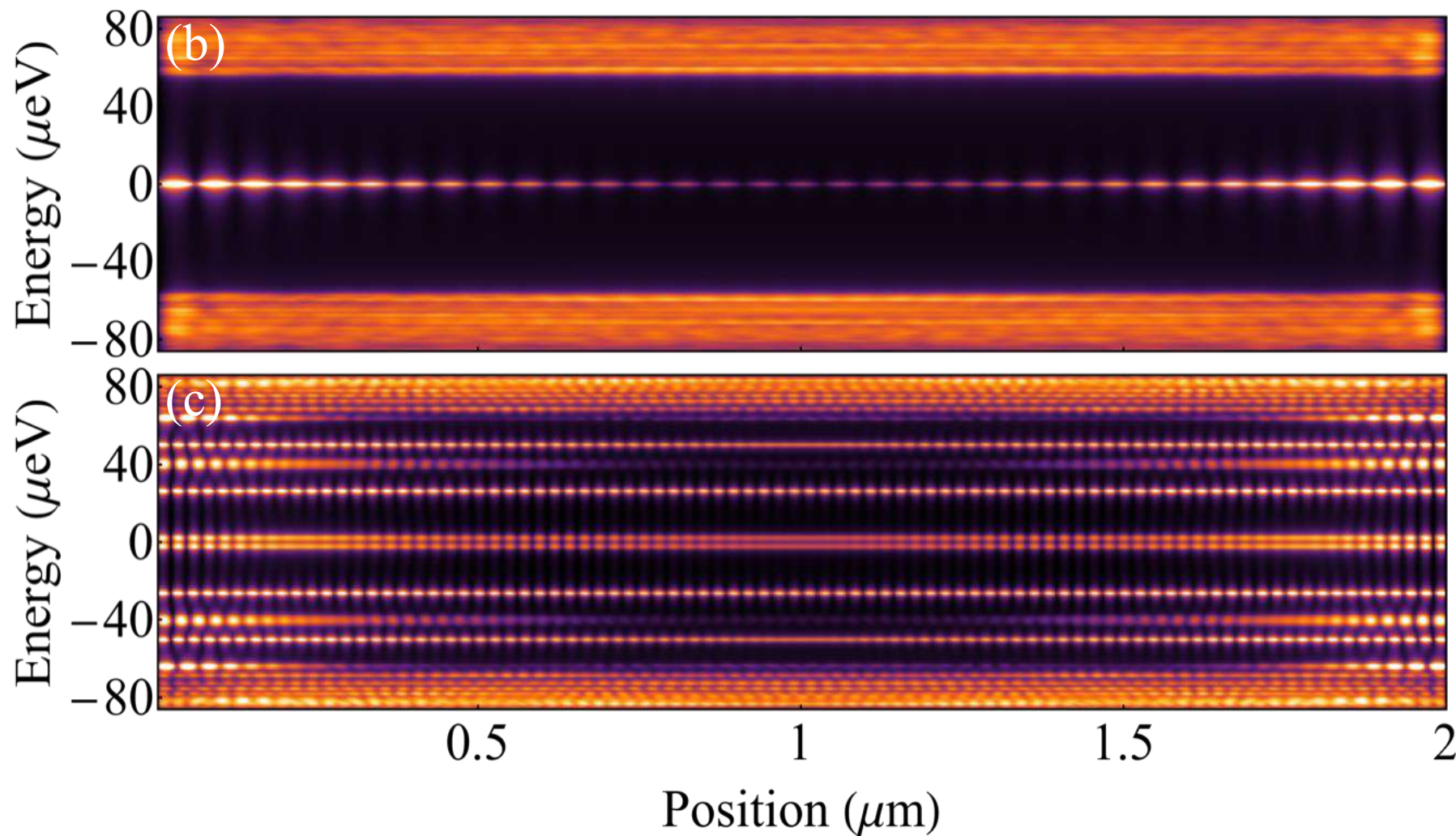


# Phase diagrams (clean systems)





# Finite size effects (clean finite JJ): LDOS

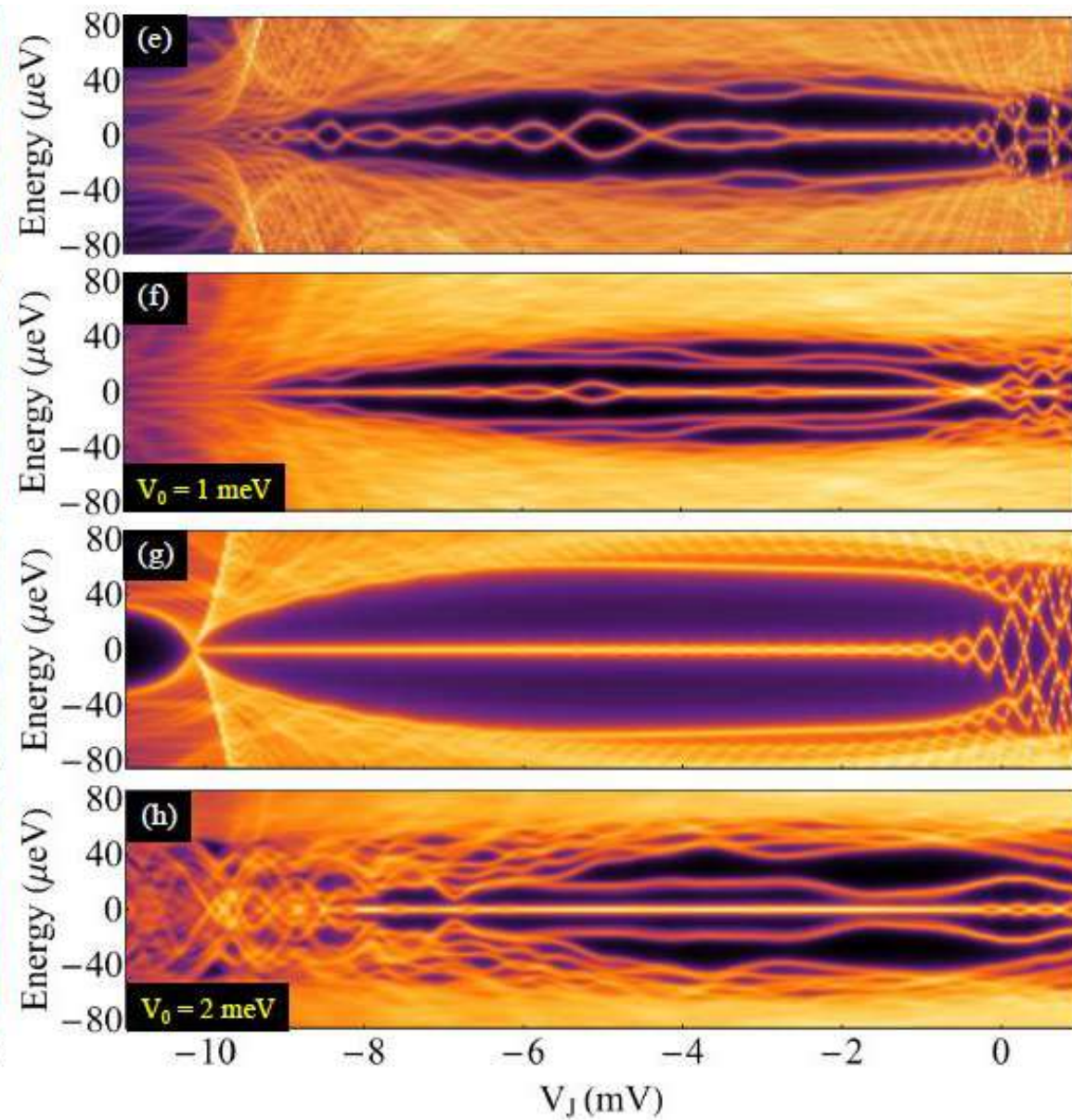
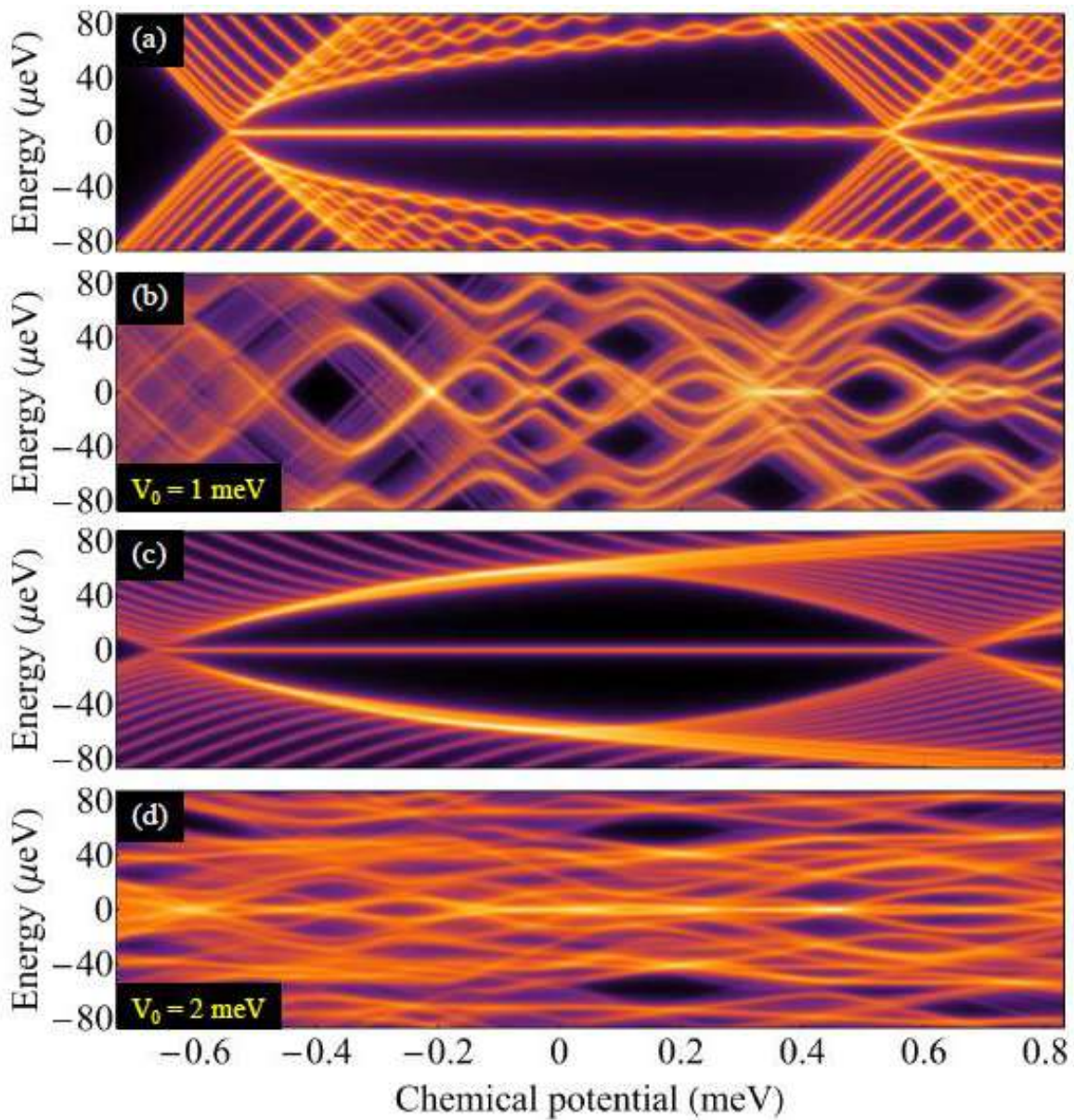




# Systems with SM disorder

Majorana wire

JJ device



$$\mu = 10$$
$$\gamma = 0.25$$

$$\mu = 10$$
$$\gamma = 0.75$$

# Topological phase diagram: Proposed approach

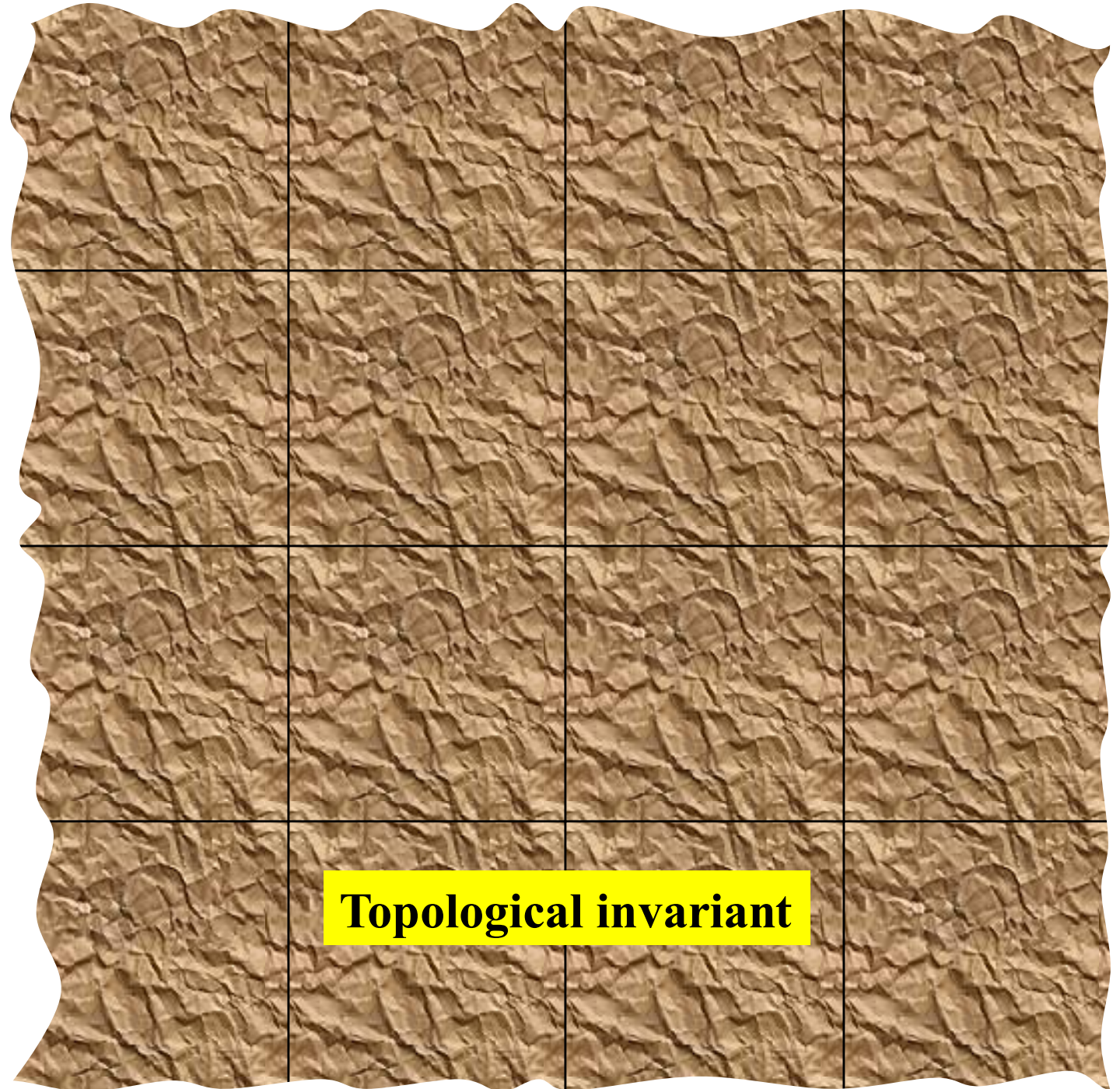
Finite disordered system



TL



Infinite system with periodic disorder

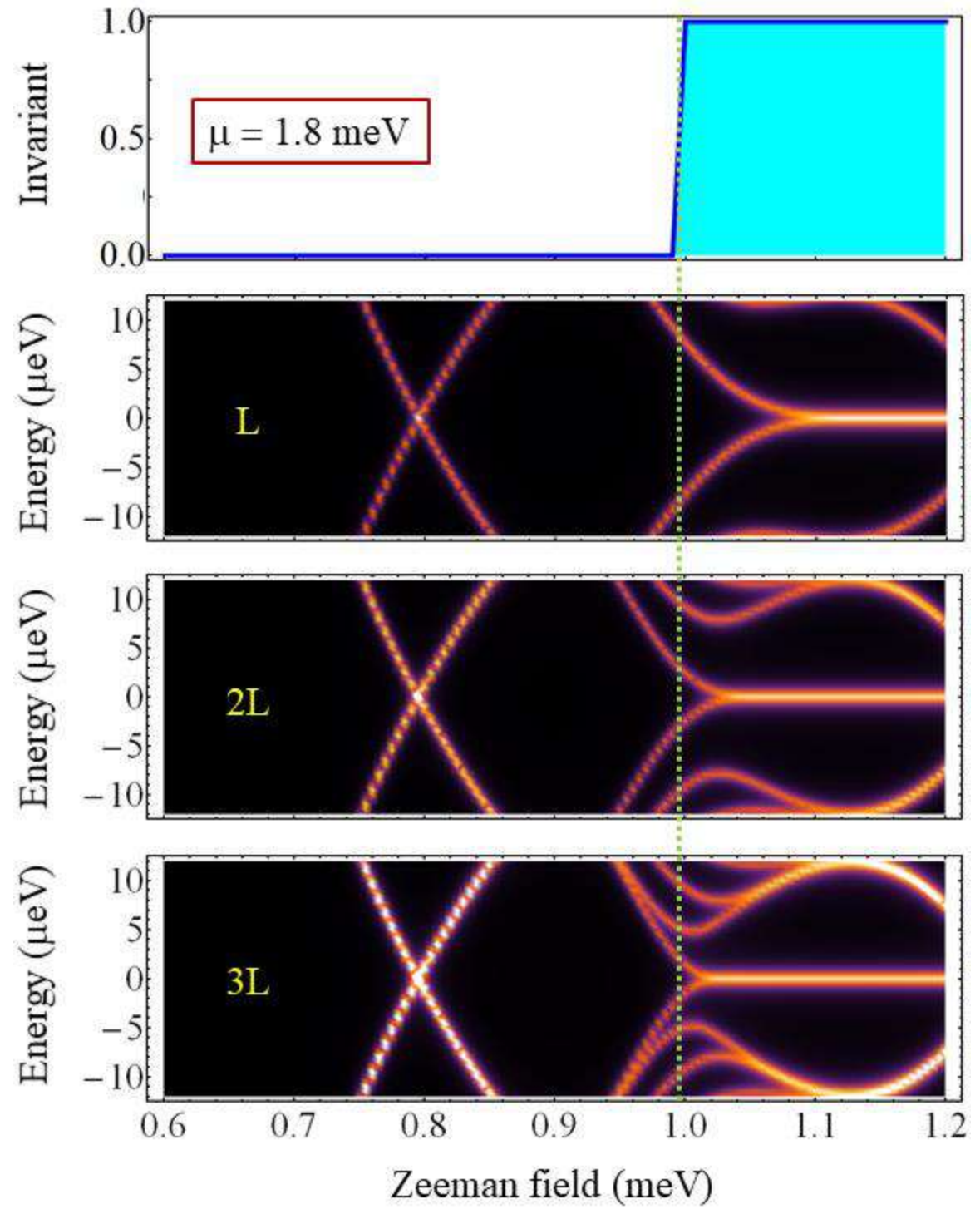
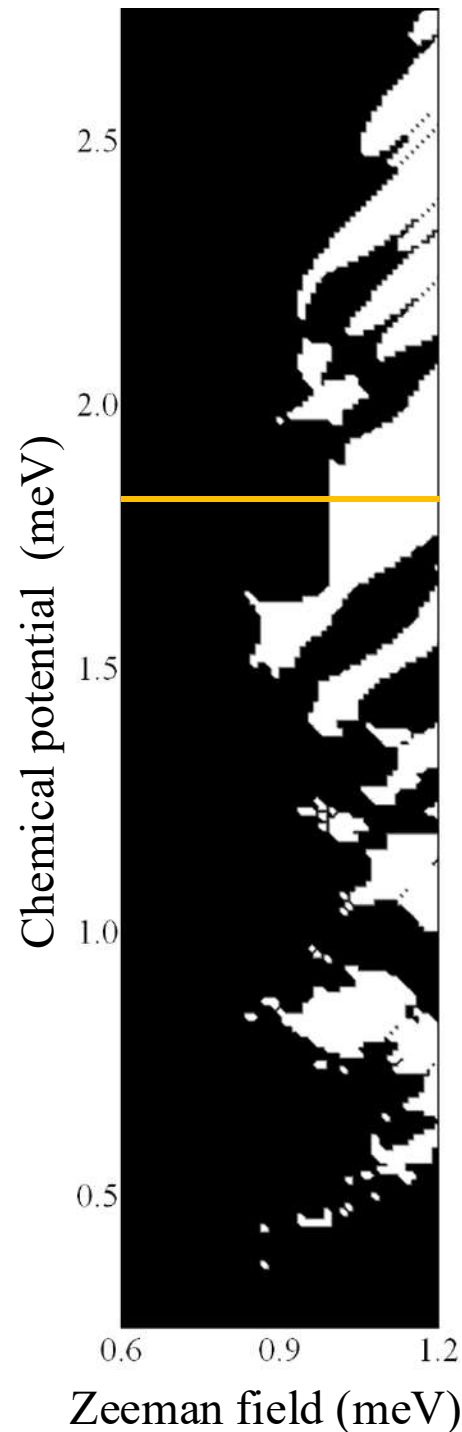


**Topological invariant**



# (Operational) topological phase

$L=4\text{ }\mu\text{m}$ ,  $V_0 = 1.5\text{ meV}$



# Summary & Conclusions

- The quasiparticle gap characterizing JJ structures is typically small; rotating the magnetic field leads to a proliferation of gapless SC phases
- Reducing the potential of the outside SM regions results in a nearly gapless system with a highly “fragmented” topological phase diagram
- Varying the potential in the junction region results in a crossover between a “nanowire regime” and a “Josephson junction regime”
- The topological gap has a nonmonotonic dependence on the width of the SC films, with an optimum width that depends on other system parameters (e.g.,  $\mu$ )
- Investigating the robustness of the topological phase against disorder remains a critical task